

Fabrication of nanostructures and nanoscale devices.

Part 6.

Galina A. Tsirlina

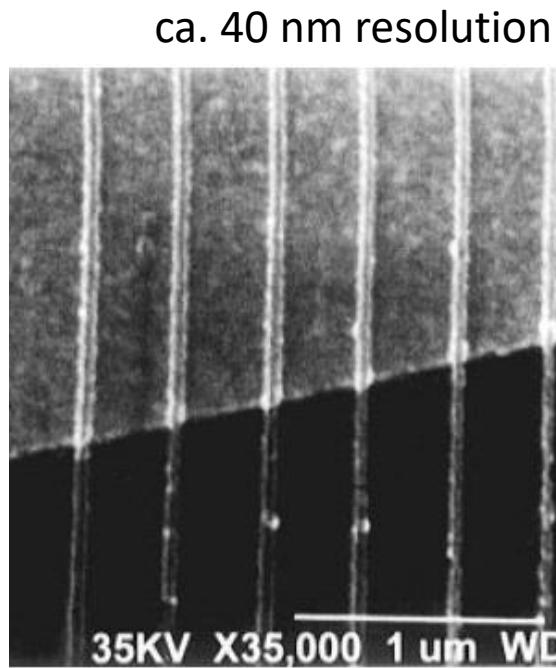
galina.tsirlina@nanocenter.si

galina.tsirlina@protonmail.com

See the lectures at <https://www.nanocenter.si/qt-future/education-2/>

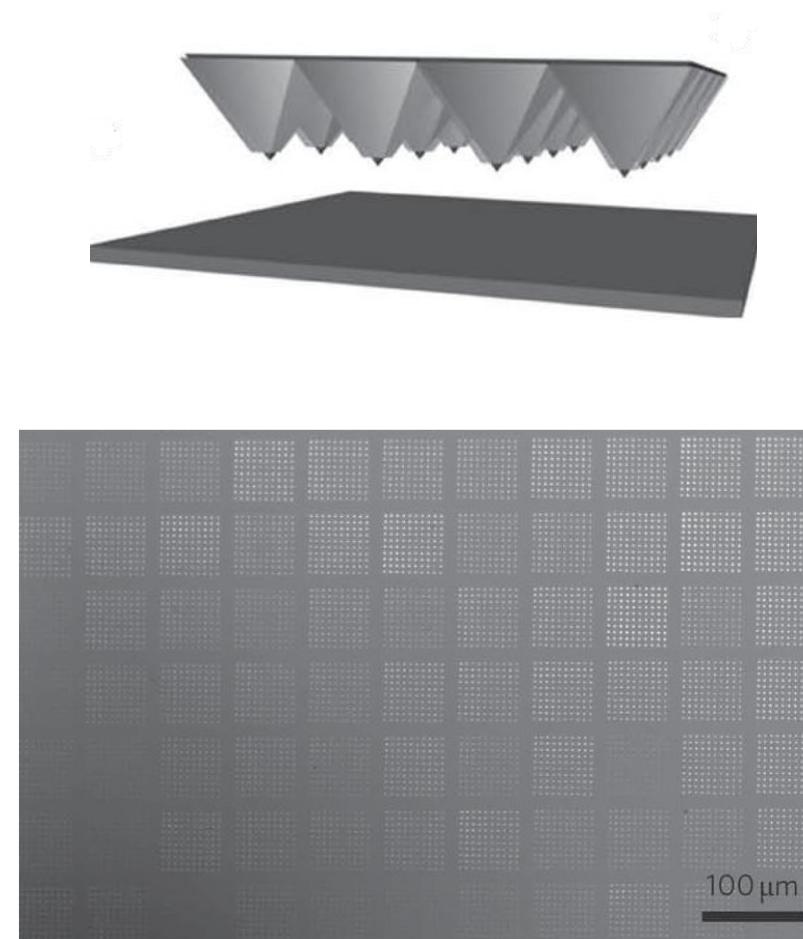
Polymers treatment in atomic force microscope (AFM) configuration

Q4

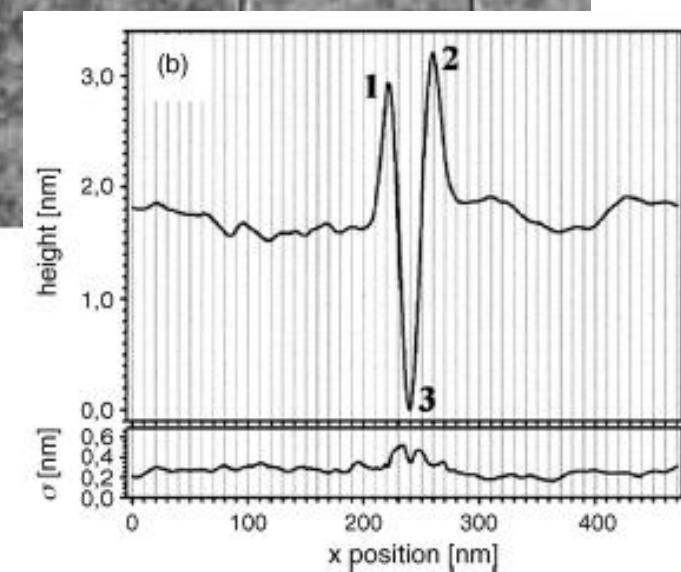
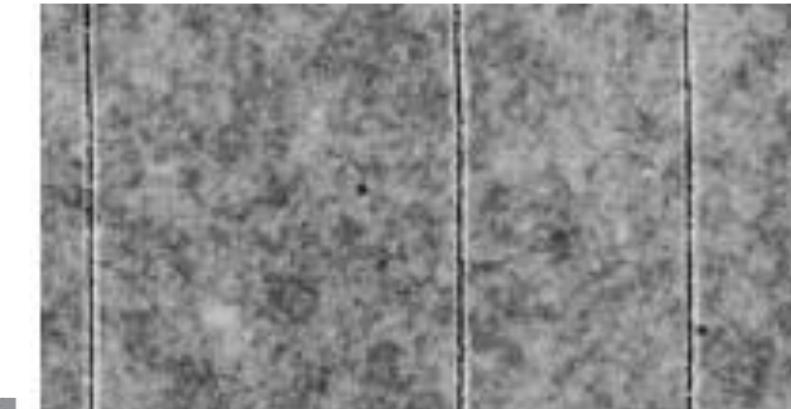


Chem. Rev. 97 (1997) 1195

Mechanical + thermal
effect on the polymers



Macromol. Rapid Commun.
33 (2012) 359



Mater. Sci. Eng. R54 (2006) 1

Principle technological schemes

Part 5 Optical and Electronic Lithography

Polymer and inorganic resists (composition, solubility, microstructure)

Spin-coating, adhesion, roughness

Light and beam interactions with positive and negative resists; amplification

Post-exposure procedures (developers, thermal effects, wetting)

Maskless lithography

Part 6 Assembling of low-dimensional objects

- Dry transfer methods

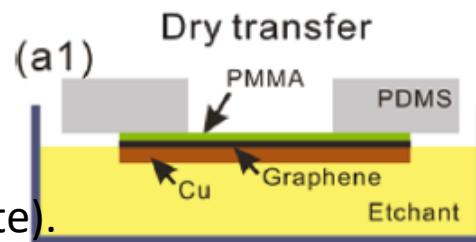
- Wet transfer methods

- Junctions, contacts

- nm-size gaps

General schemes of the transfer of a single flake (example for CVD graphene grown on Cu)

Etchant is oxidizer
(e.g. peroxodisulfate).

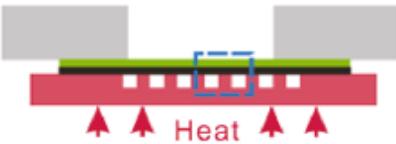


(a2)



Polymers are deleted
by heating (PDMS is
polydimethylsiloxane;
PMMA is polymethyl
methacrylate).

(a3)

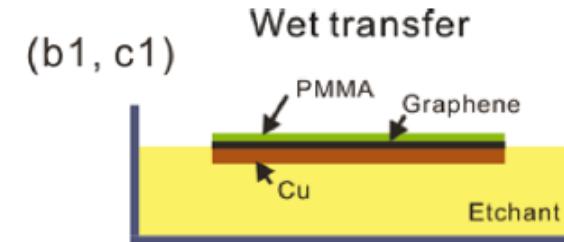


Perforated supports
- decrease flake-support
interaction;
- allow transmission
microscopy;
- are helpful to
delete traces of
liquid

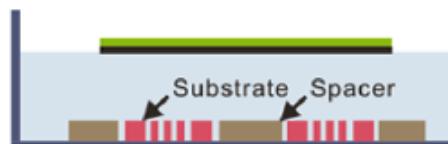
(a4)



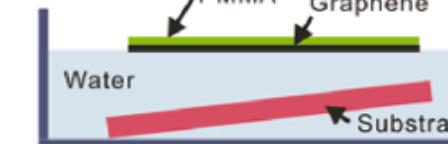
(a5)



(b2)



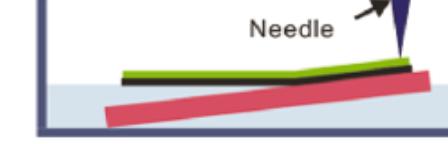
(c2)



(b3)



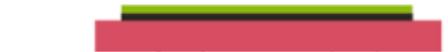
(c3)



(b4)



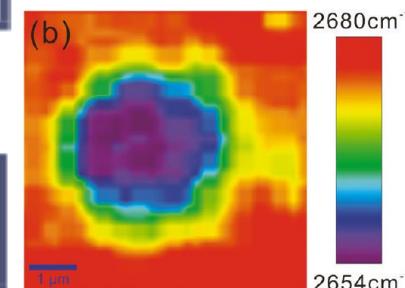
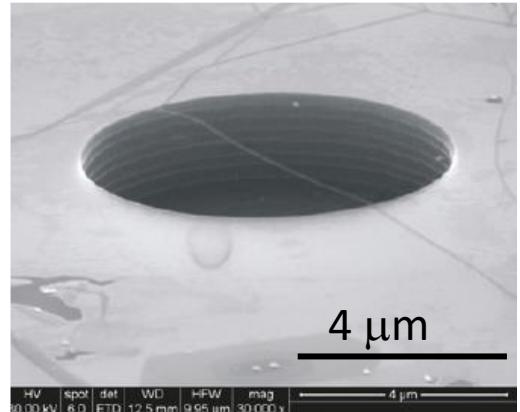
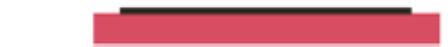
(c4)



(b5)

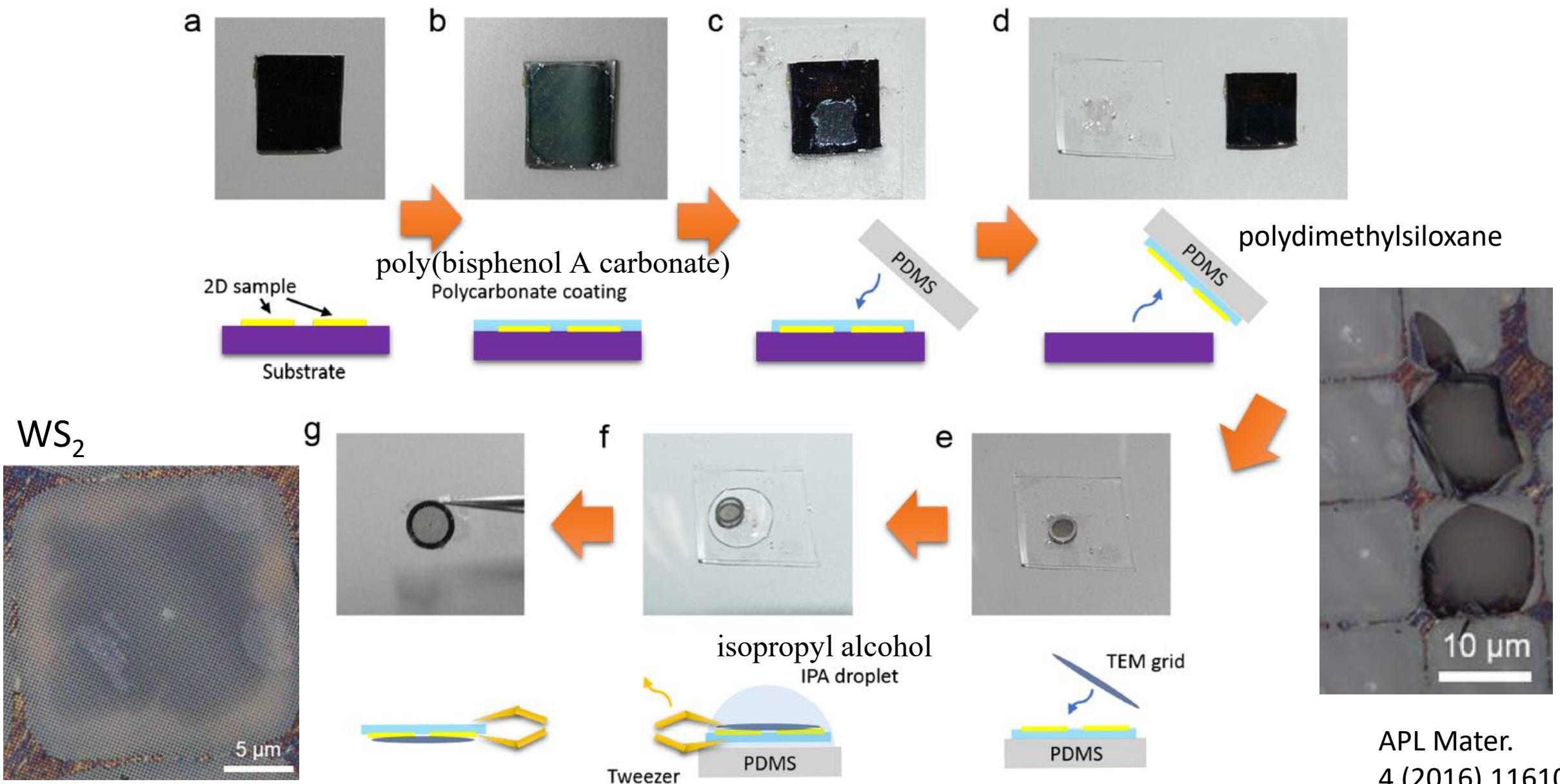


(c5)

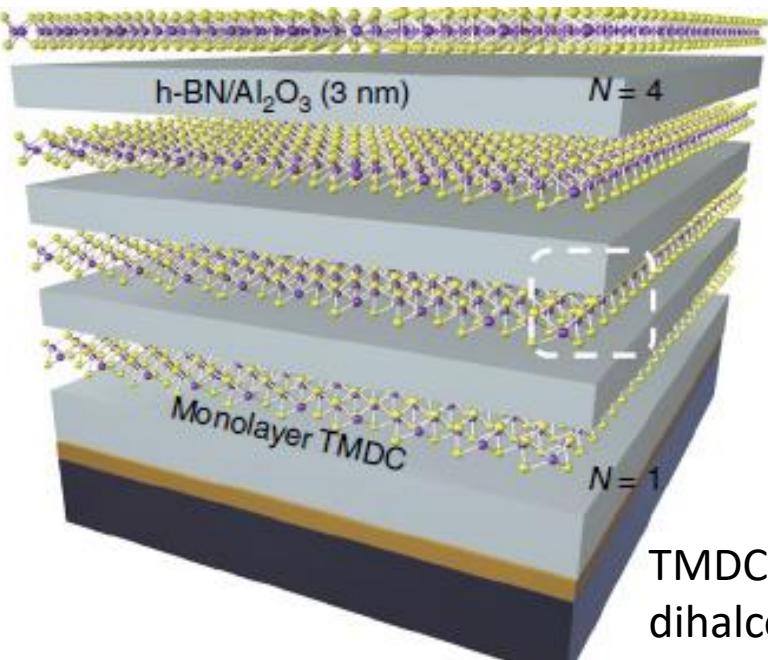


Strain near edges
of holes (Raman
mapping)

Transfer of a single flake avoiding etching (example of transfer to TEM grid)

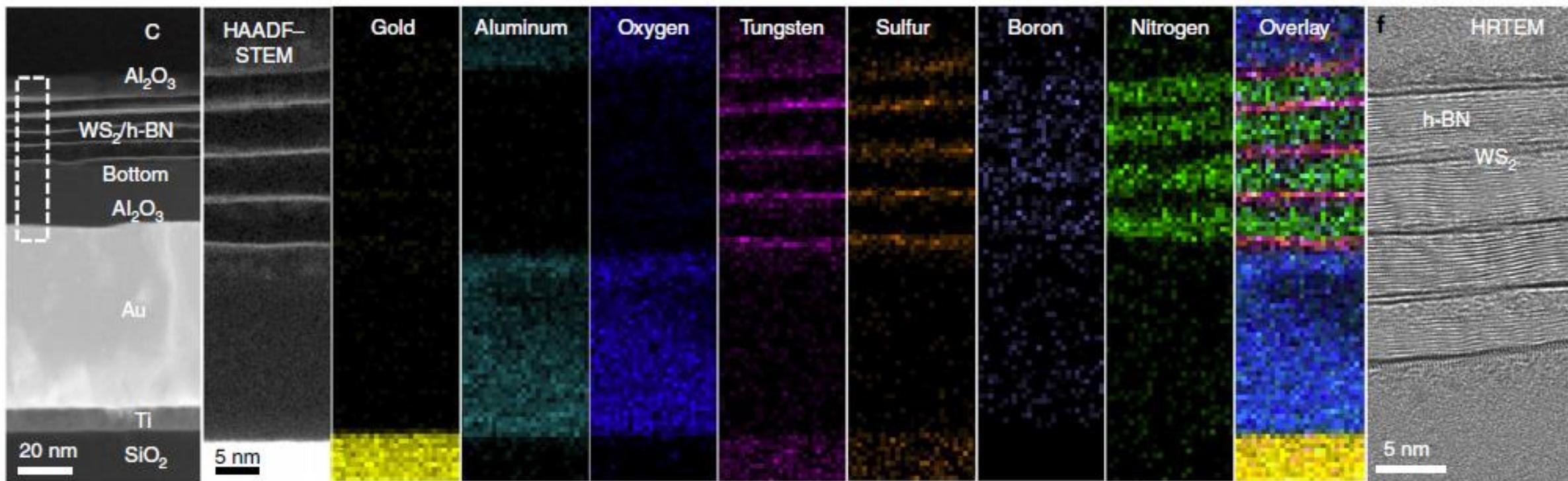
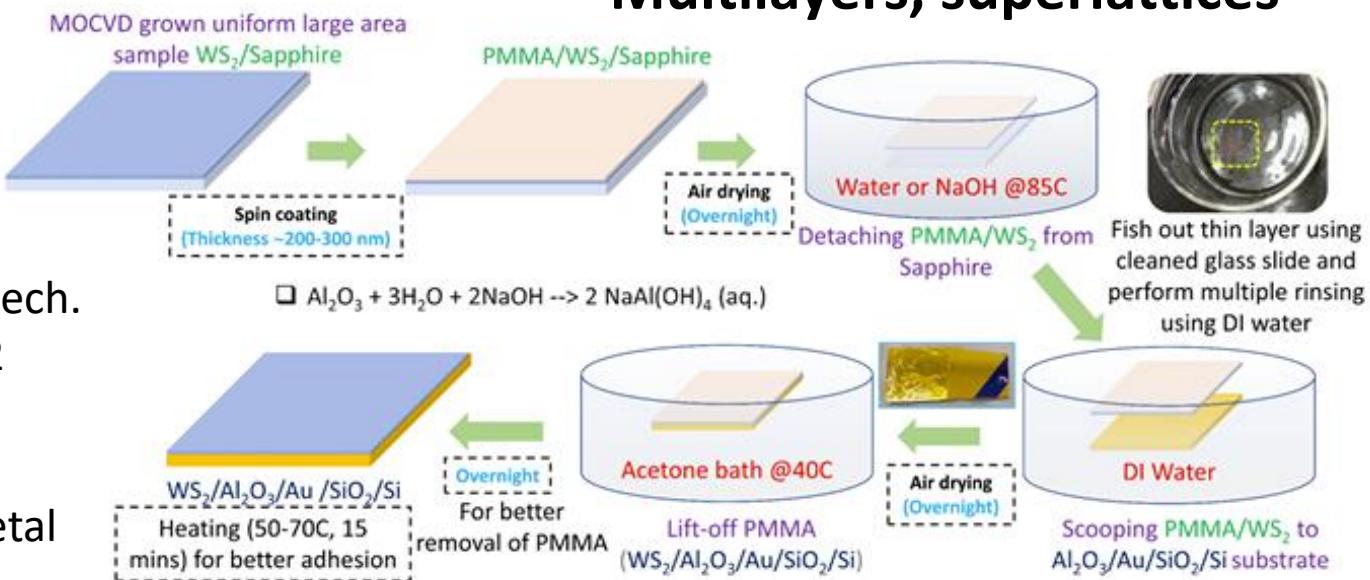


Multilayers, superlattices



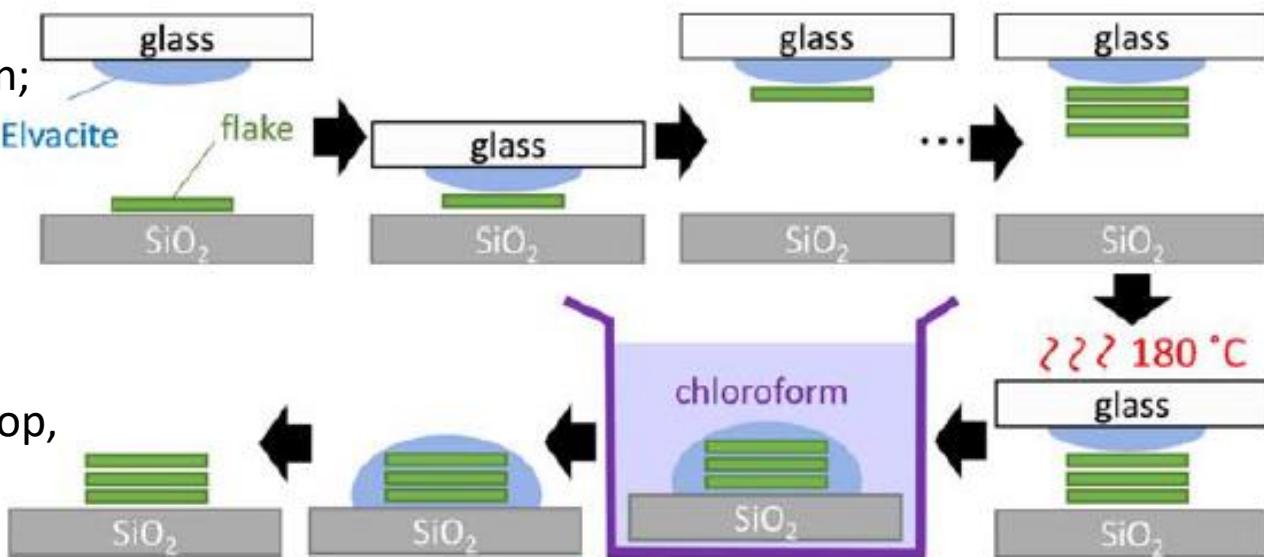
Nature Nanotech.
17 (2022) 182

TMDC = transition metal dihalogenides (MX_2)

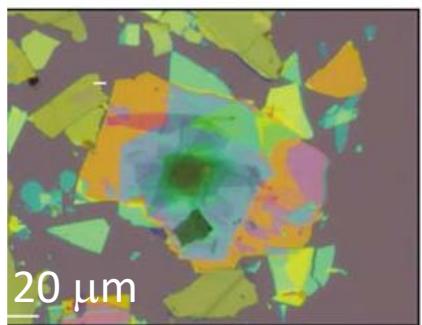


“Pick-up” approach to stacking

Elvacite is acrylic resin;
propylene carbonate based polymers can be used as well.



Jap. J. Appl. Phys. 59 (2020) 010101

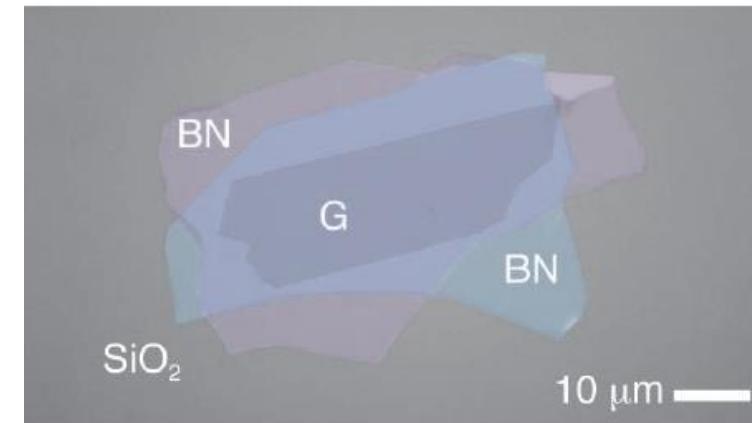
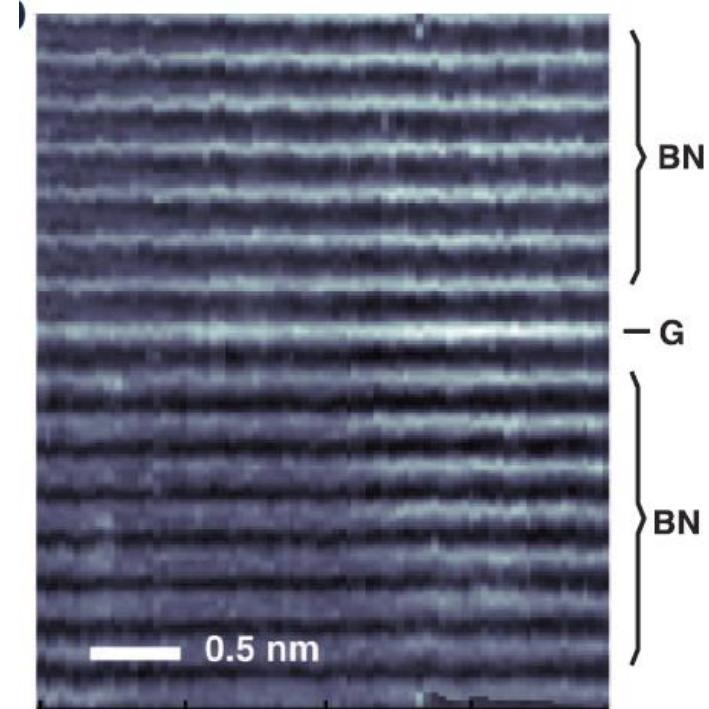


Jap. J. Appl. Phys.
59 (2020) 010101

Dozens of flakes can be stacked, but the size of each flake is occasional.

Optical microscopy is required to combine the central parts of all flakes.

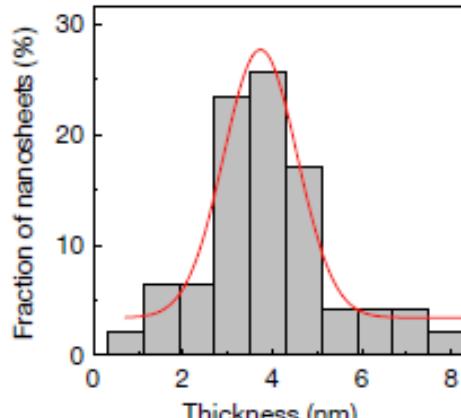
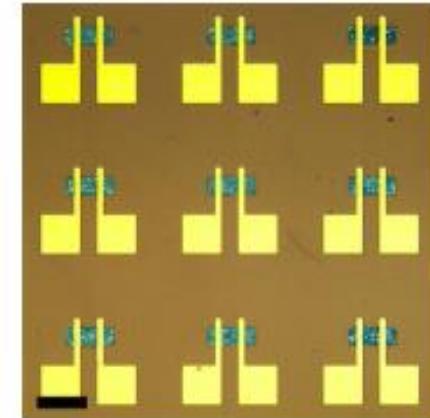
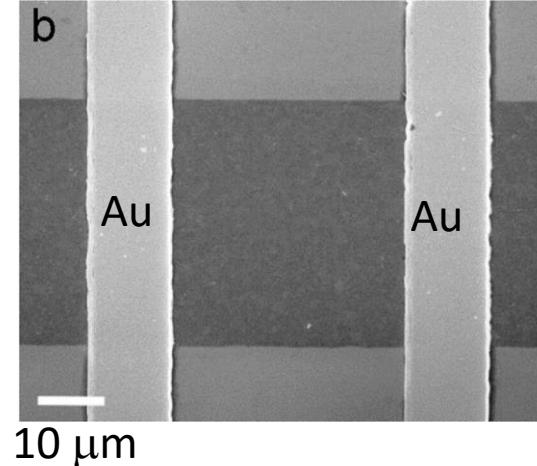
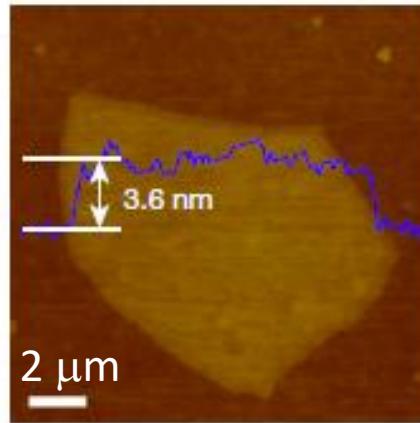
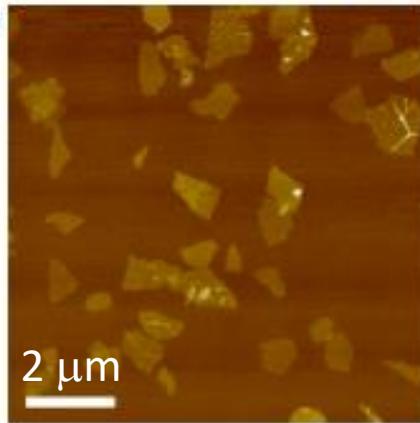
Automatic tools are already developed, but all **single-flake technologies** still work **mostly for laboratory prototype devices**.



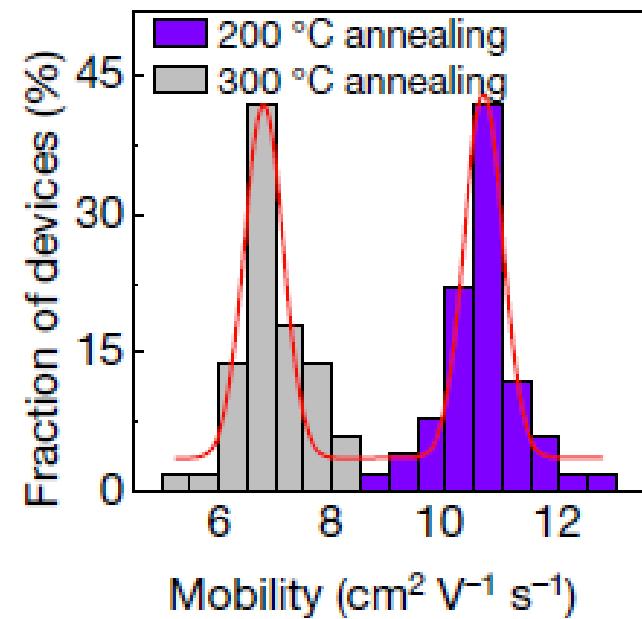
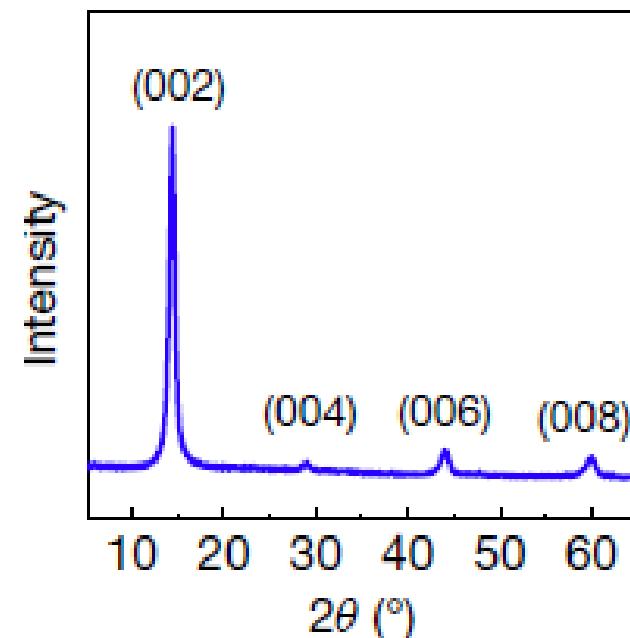
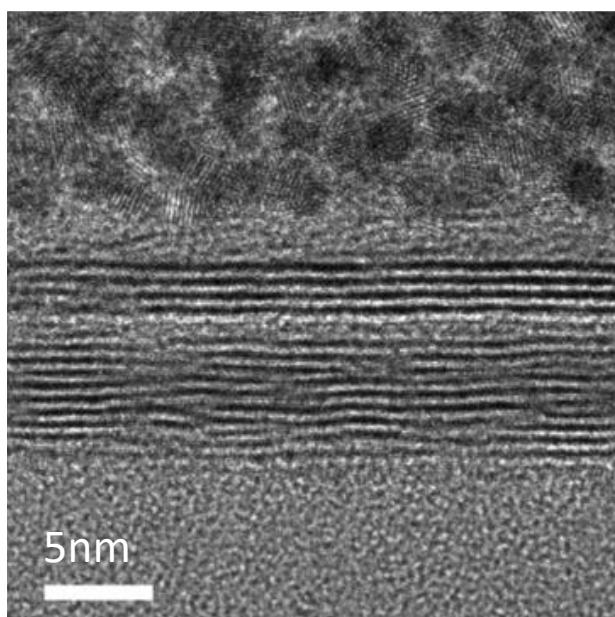
Science 342 (2013) 614-617

Ink-based assembling of 2D flakes (several atomic layers): simple, suitable for any support

Suspension spin-coating, then lithography

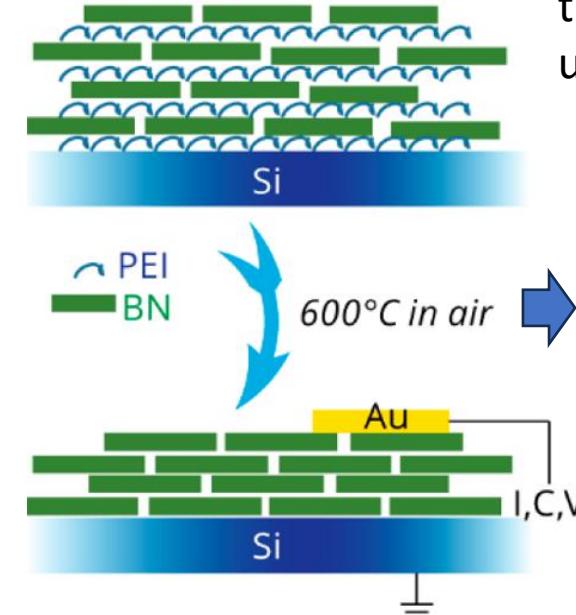
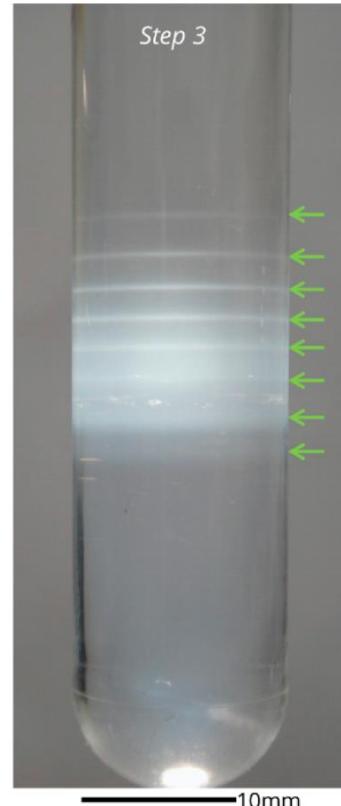
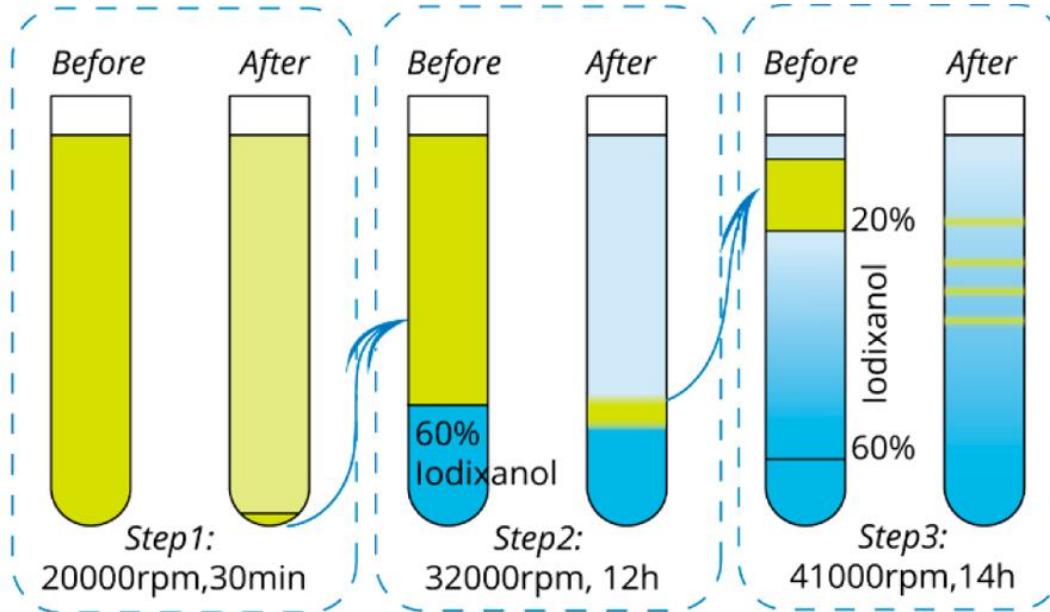


(0.61 nm/layer)

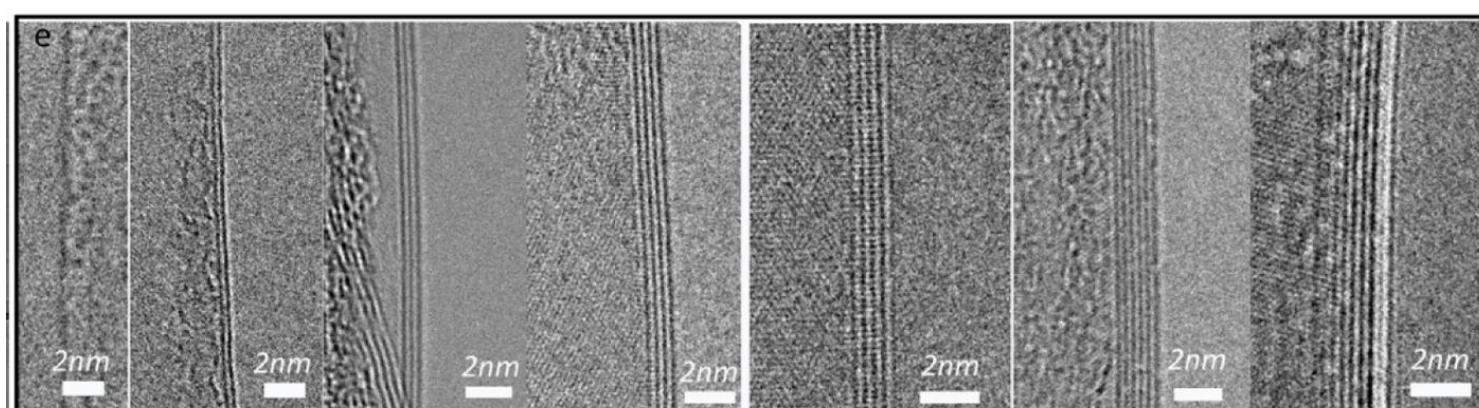
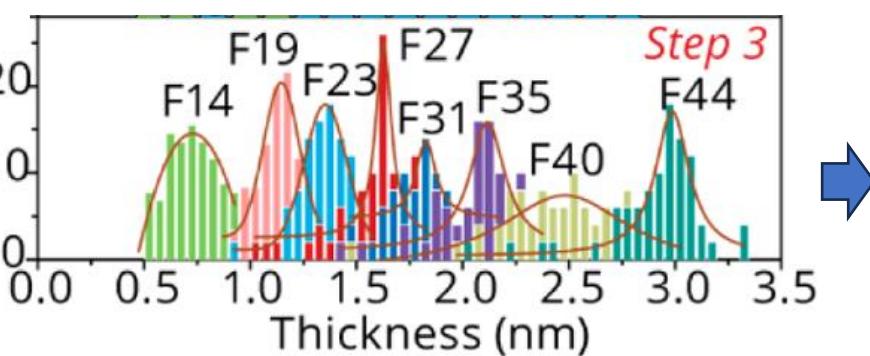


Ink-based assembling of 2D flakes: size/thickness sorting

Centrifugation + extraction, hexagonal BN:

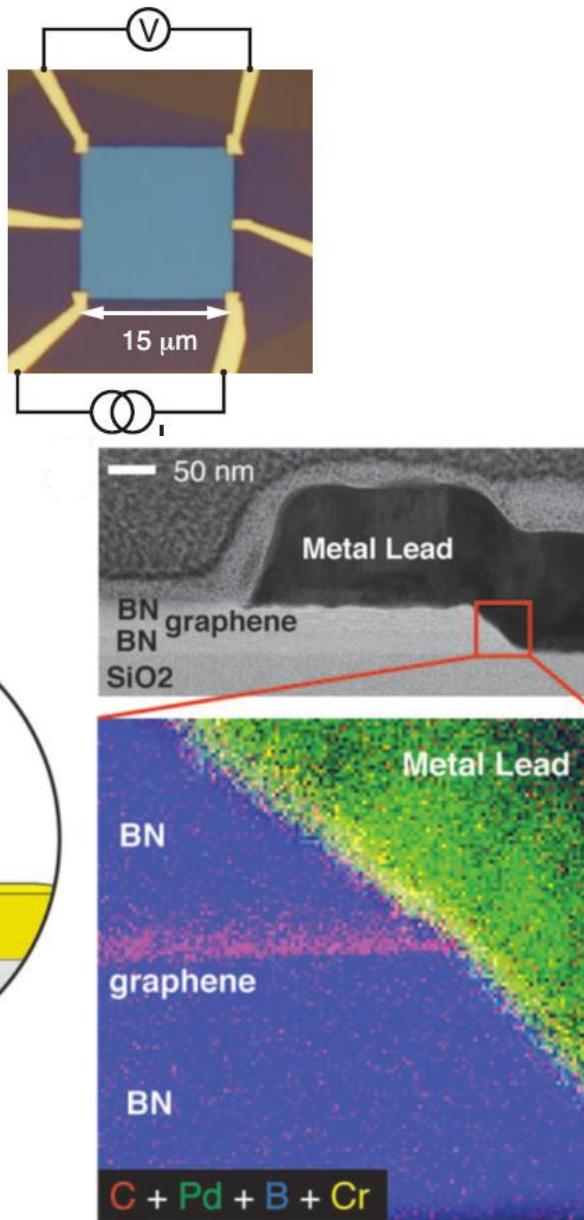
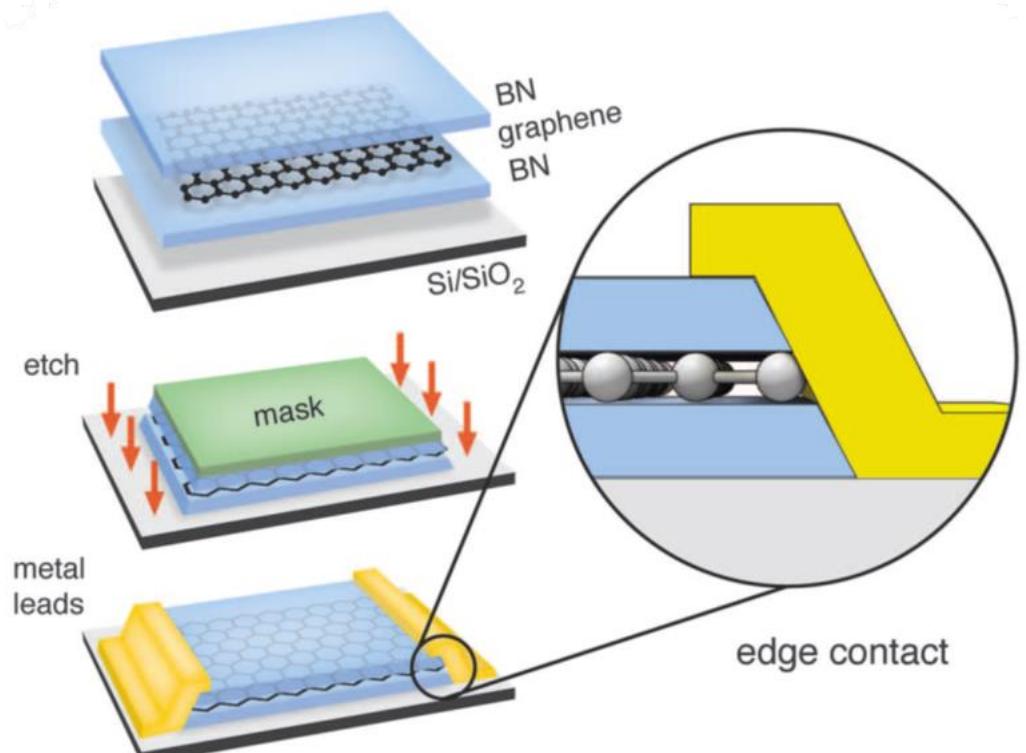


CVD Graphene is transferred from Cu foil using polymer resist

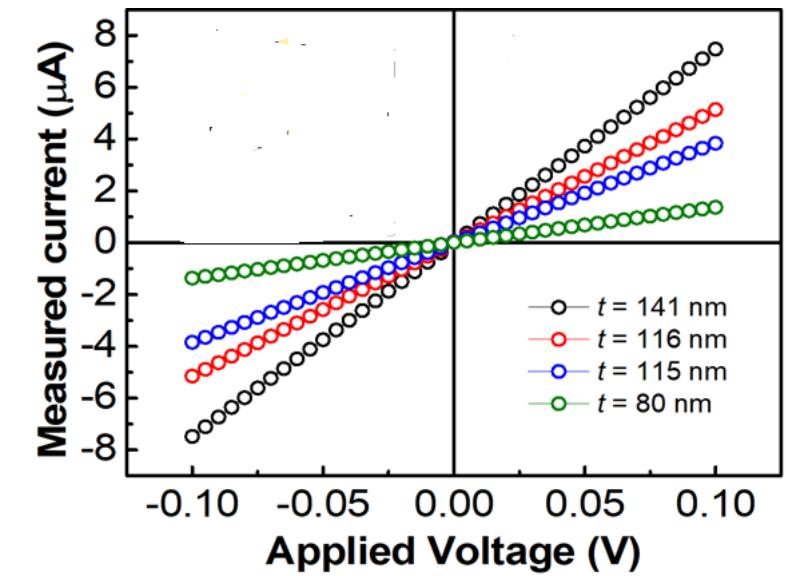
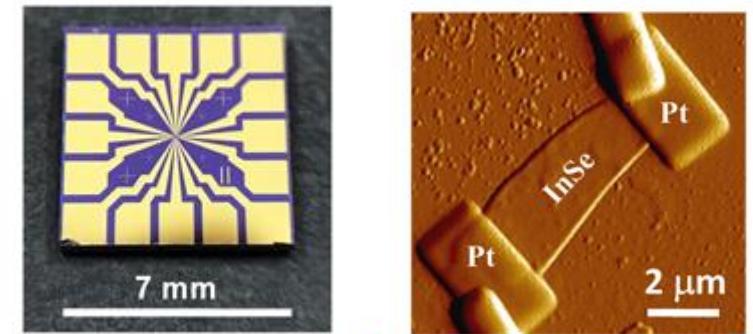


1....7 layers

Edge-contacts to 2D structures



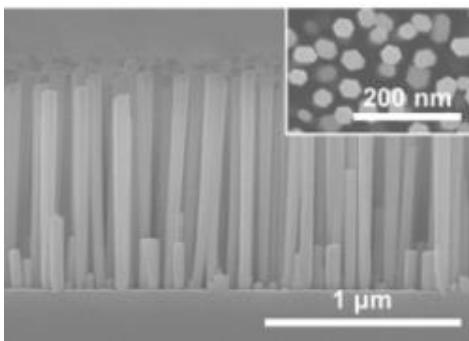
Contacts formed using focused ion beam (FIB)



Structures containing the fragments of various dimensions: 2D and 1D

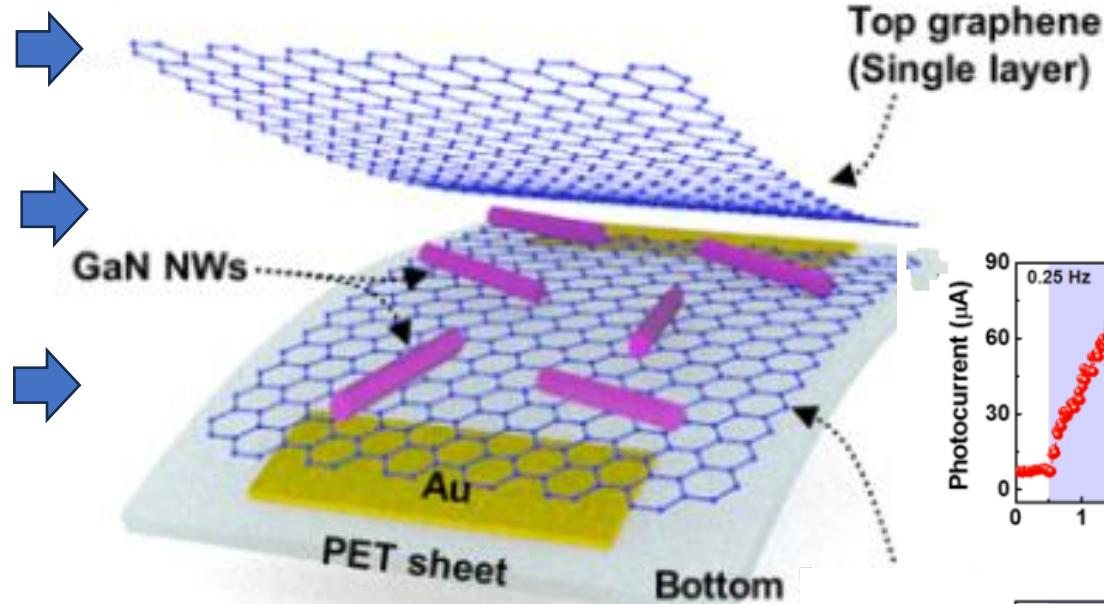
Au sputtering on flexible support
(PET = polyethylene terephthalat),
1x0.5mm²x27nm; **60 µm** between
two Au contacts.

Graphene, up to 3 layers,
wet transfer.

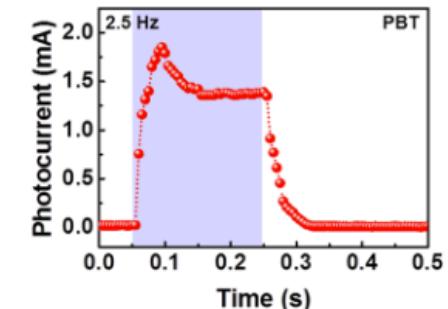
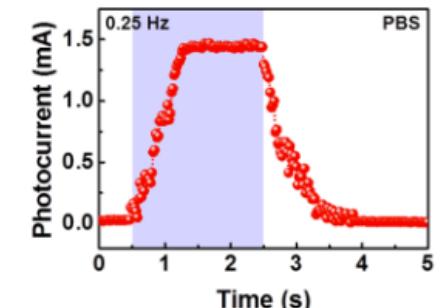
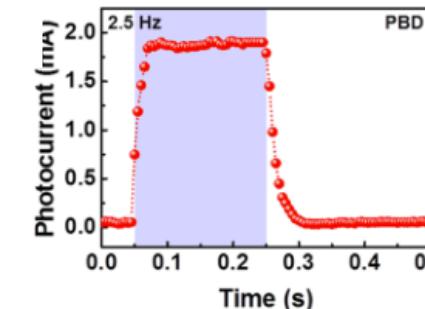
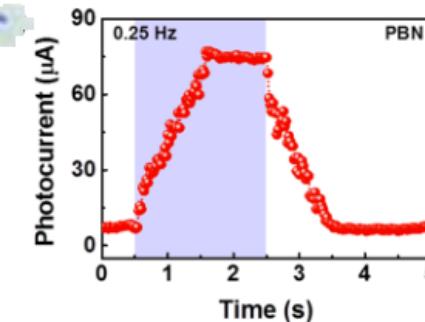
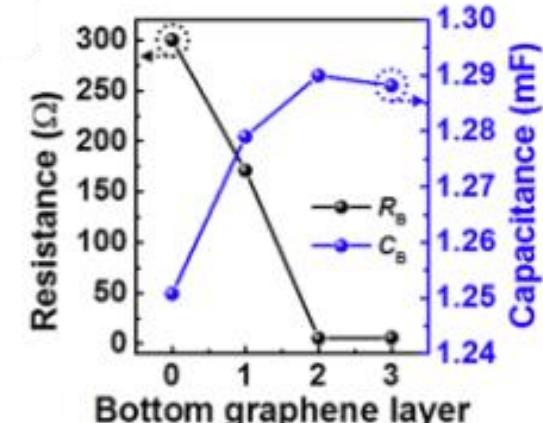


GaN wires grown on Si:
- **suspended**,
- randomly deposited.

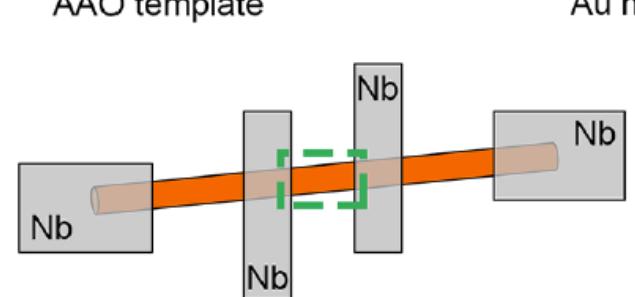
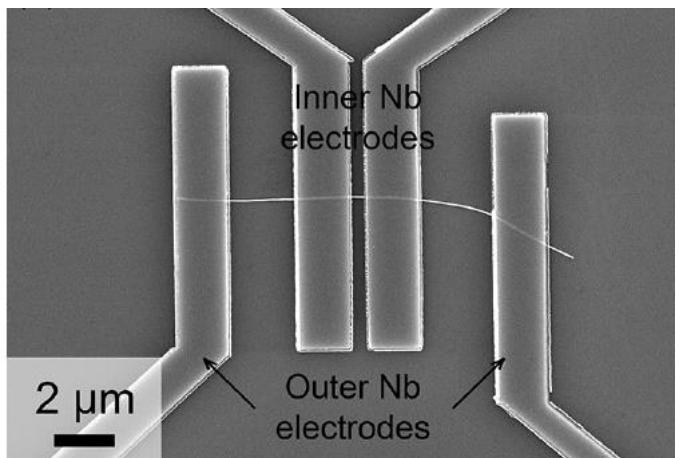
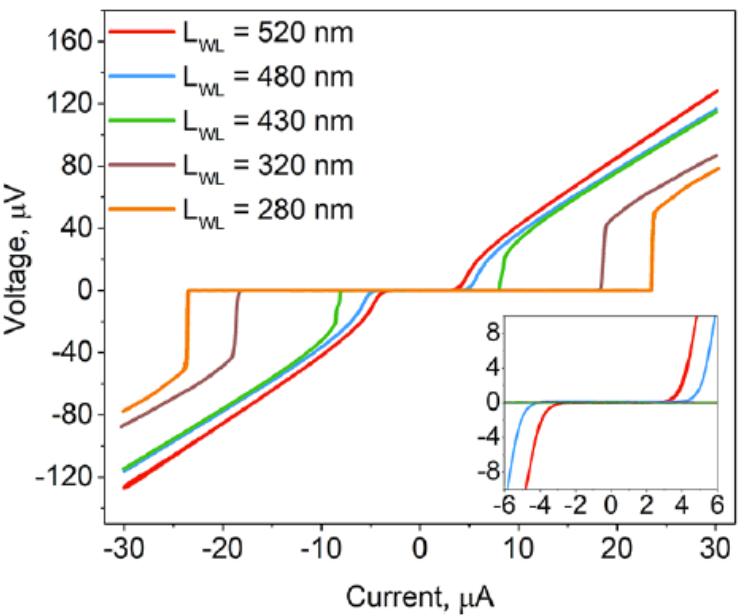
ACS Appl. Mater. Interfaces
12 (2020) 970



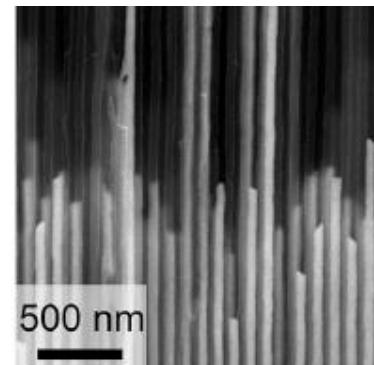
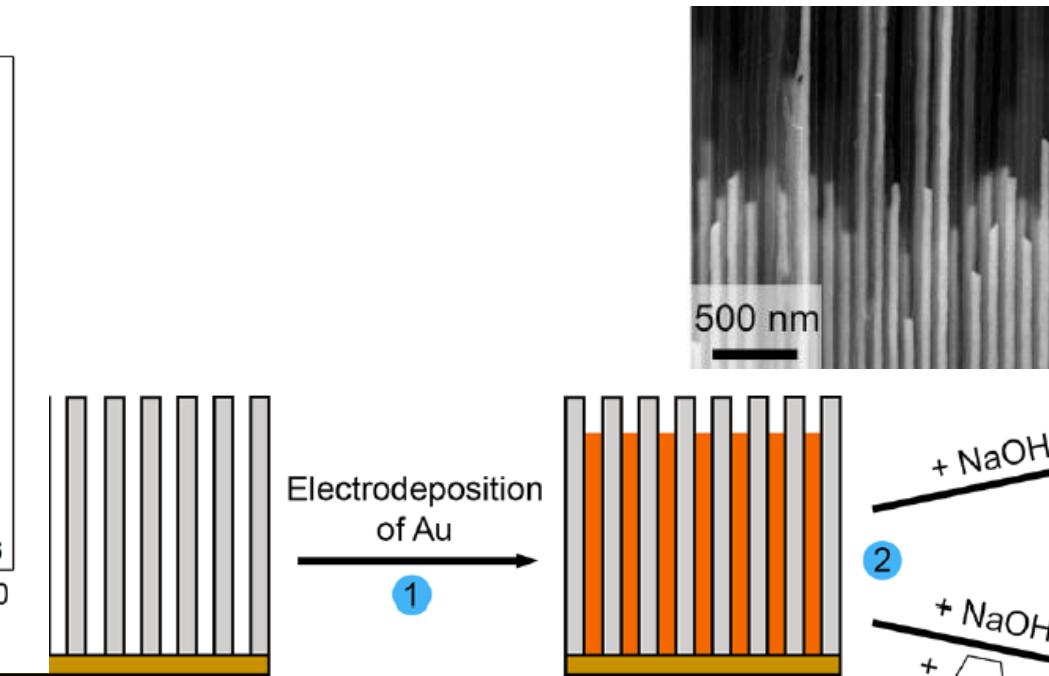
layers of graphene:
0 (PBN), 1 (PBS),
2 (PBD), 3 (PBT)



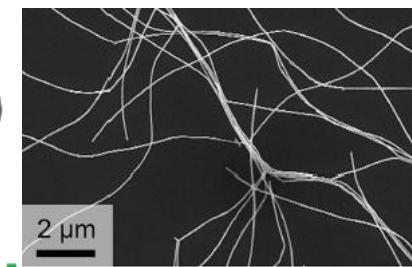
Single wire devices requiring contacts (example of Josephson junction)



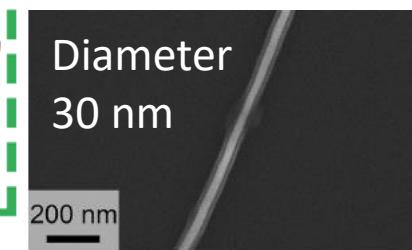
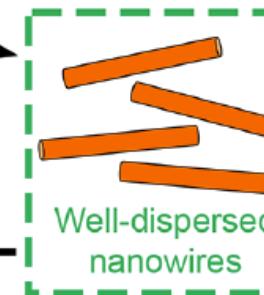
Josephson junction with a single Au nanowire
as a **weak link**



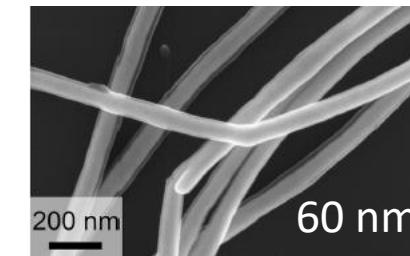
after AAO dissolution, surfactants are necessary to suppress wires aggregation; in this example, polyvinylpyrrolidone (PVP) is applied as surfactant



Aggregated nanowires



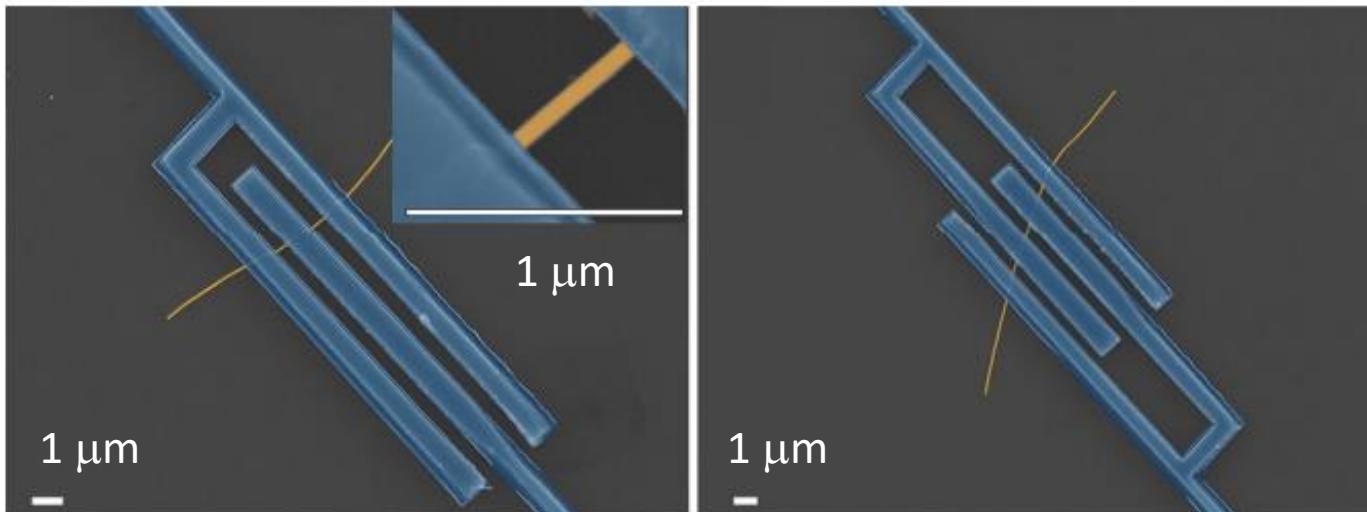
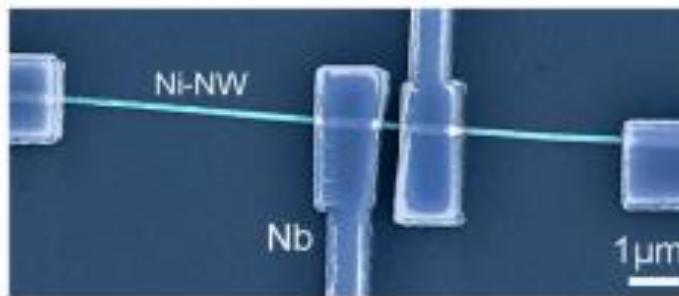
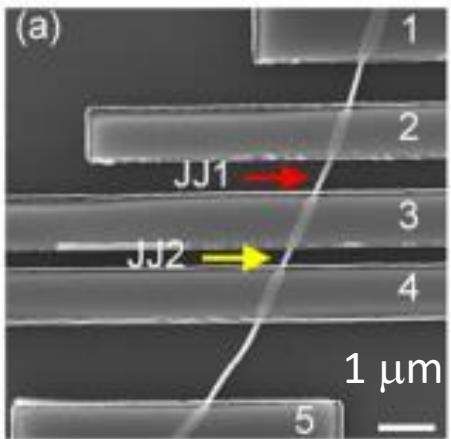
Diameter
30 nm



60 nm

Single wire devices ... macroscopic contacts

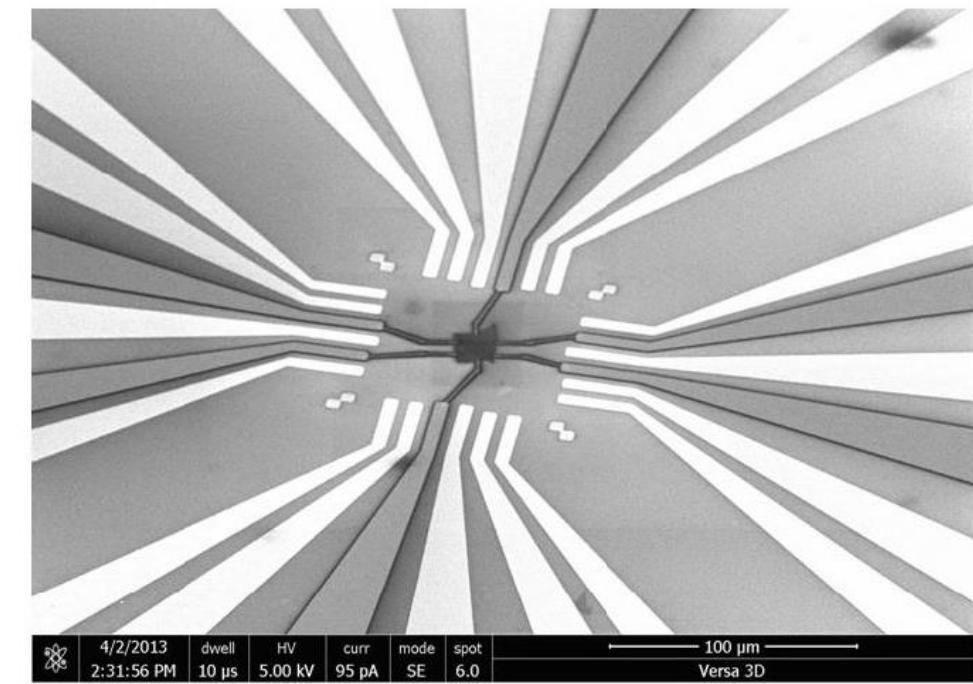
Sci. Rep. 9 (2019) 14470;
11 (2021) 17042



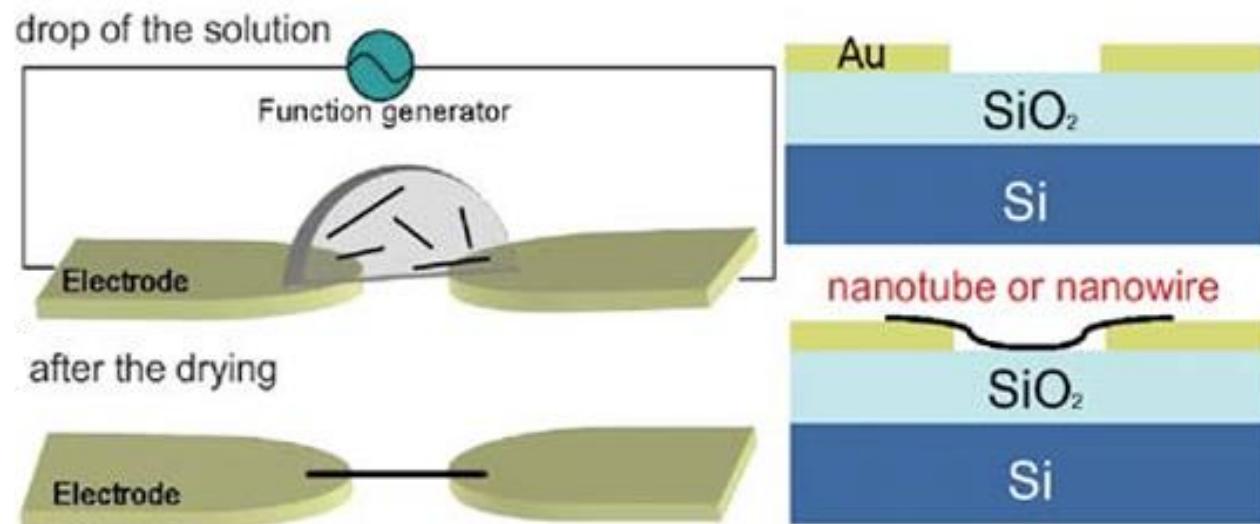
Macroscopic bonding (welding)



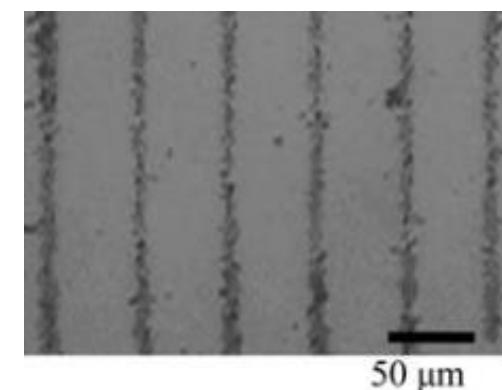
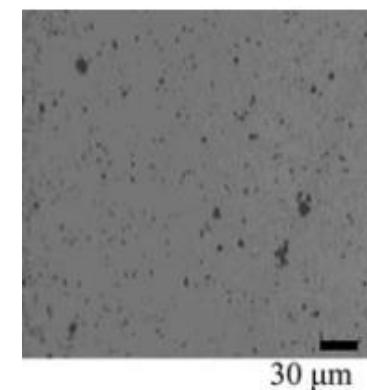
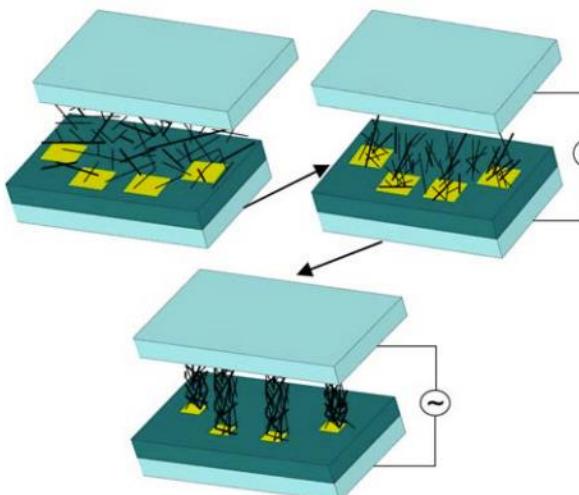
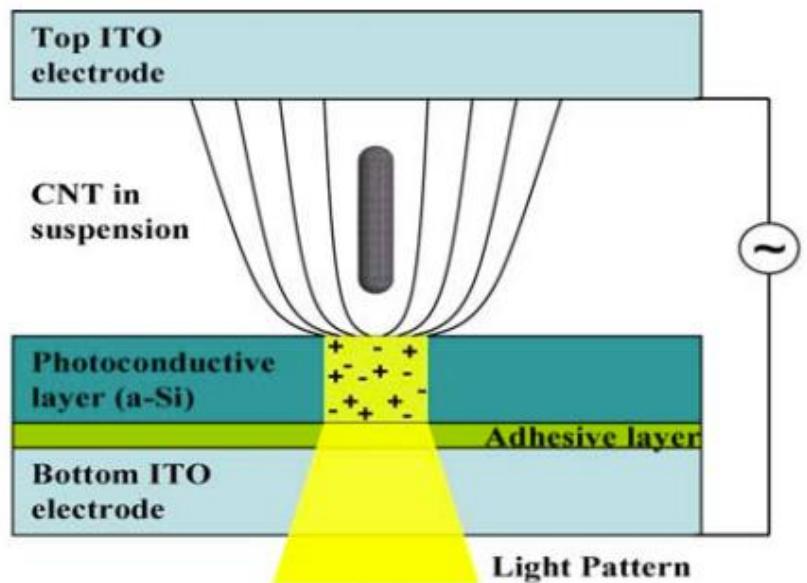
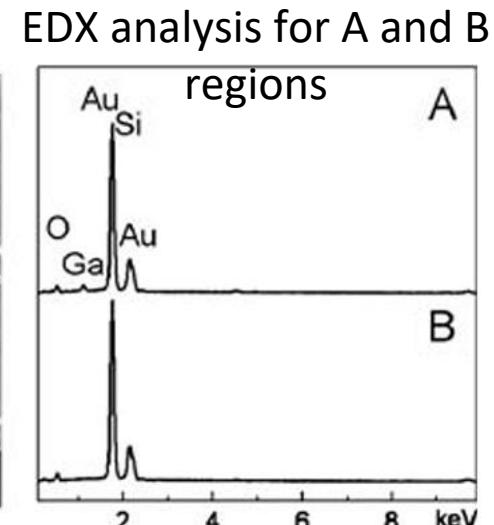
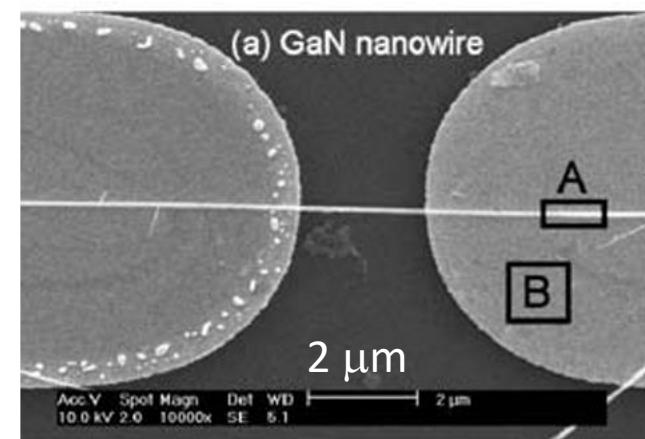
Macroscopic contact pads



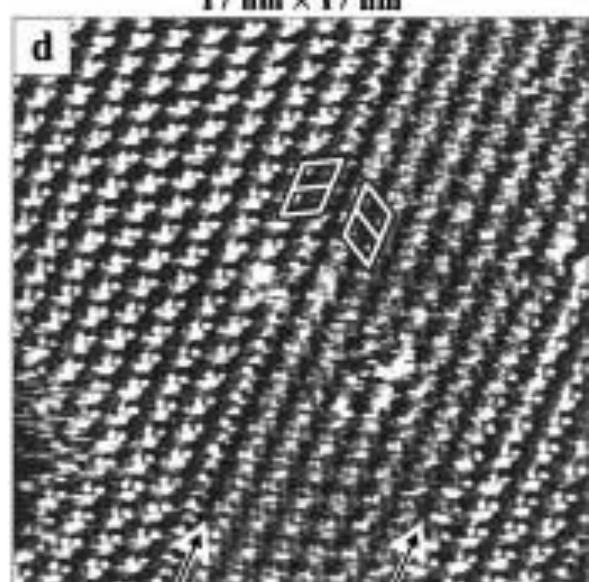
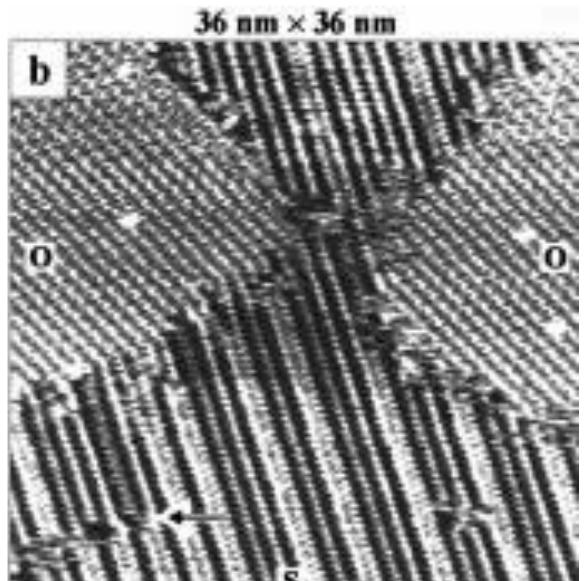
Electrophoresis as manipulation tool for 1D fragments



Curr. Appl. Phys. 6, Suppl. 1
(2006) e216-e219

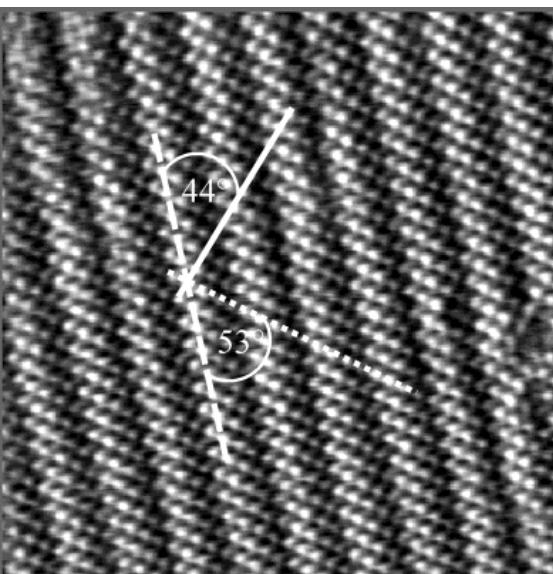


Thiols (R-SH): molecular linkers for surfaces and 0D fragments (nanoparticles)



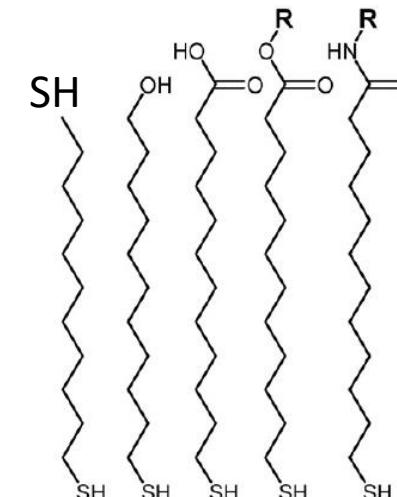
↙ Ethane thiol on Au(111)
Butane thiol on Au(100)

↓ 15x15 nm²

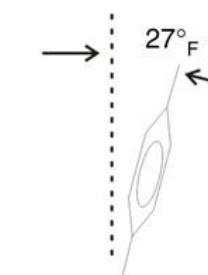


↙ Mirror domains

Langmuir 15 (1999) 2435;
19 (2003) 830



From solution:



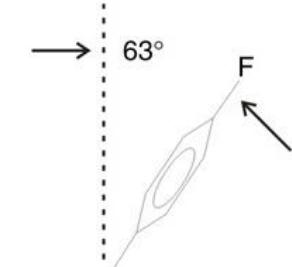
Au (111)

Surface coverage affects orientation
(tilt angle)

- SH groups and terminal functional groups of one and the same molecule can link to support surface and to nm-size particle respectively

very usual linkers are dithiols

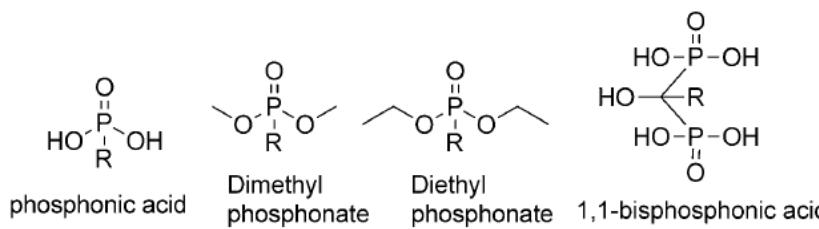
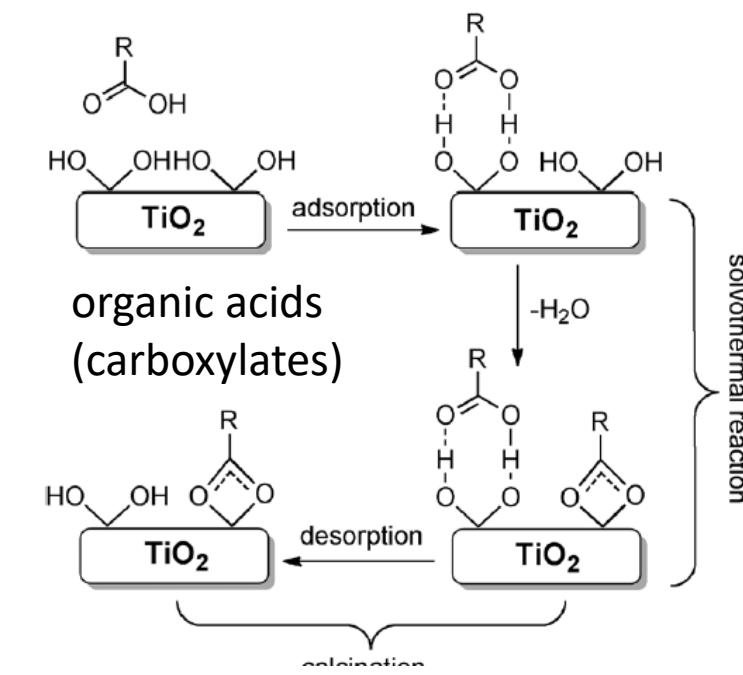
From vapor:



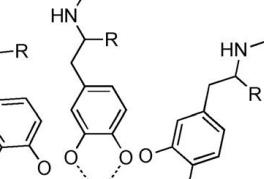
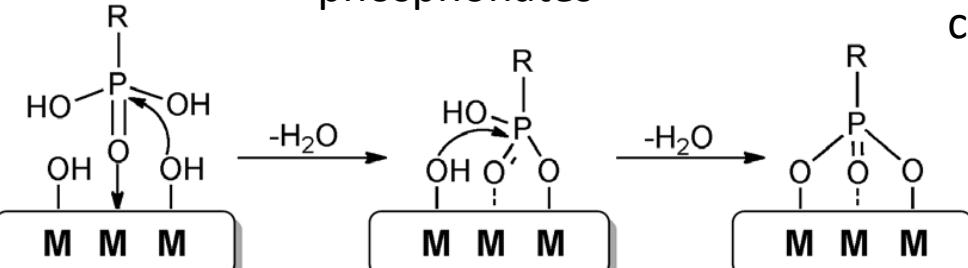
Au (111)

Surface Sci. Rep. 63 (2008) 465

Molecular linkers for oxide surfaces (when thiols are less effective)

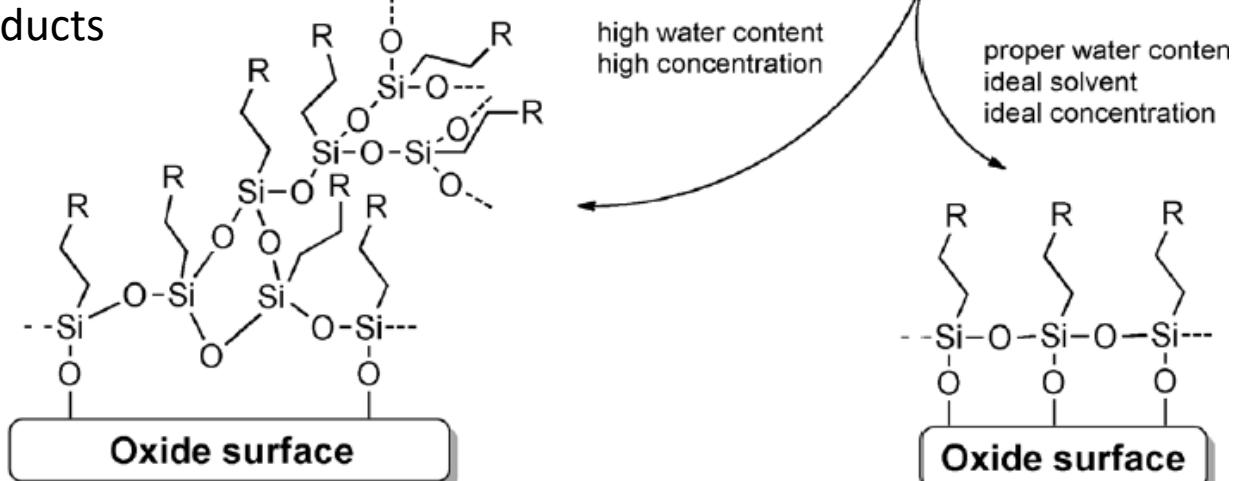
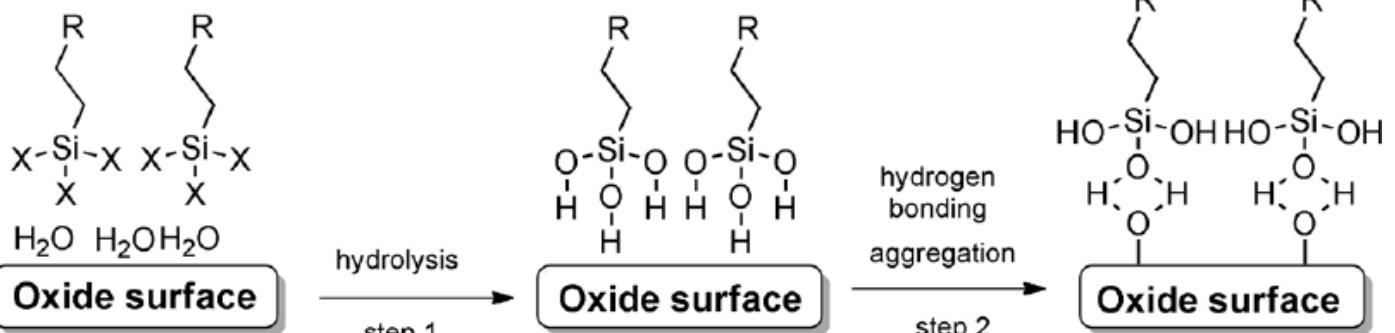


phosphonates



catecholes

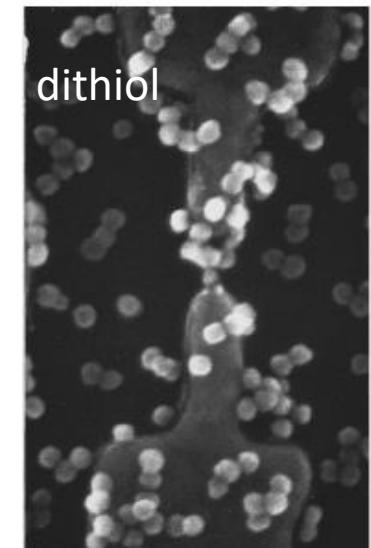
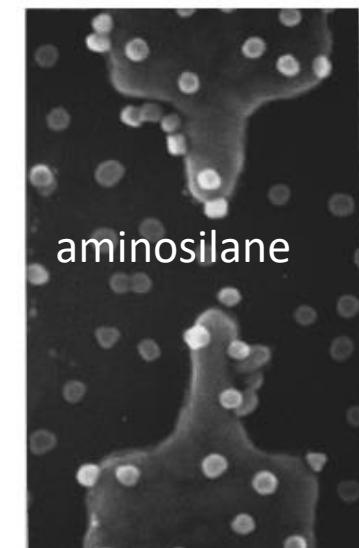
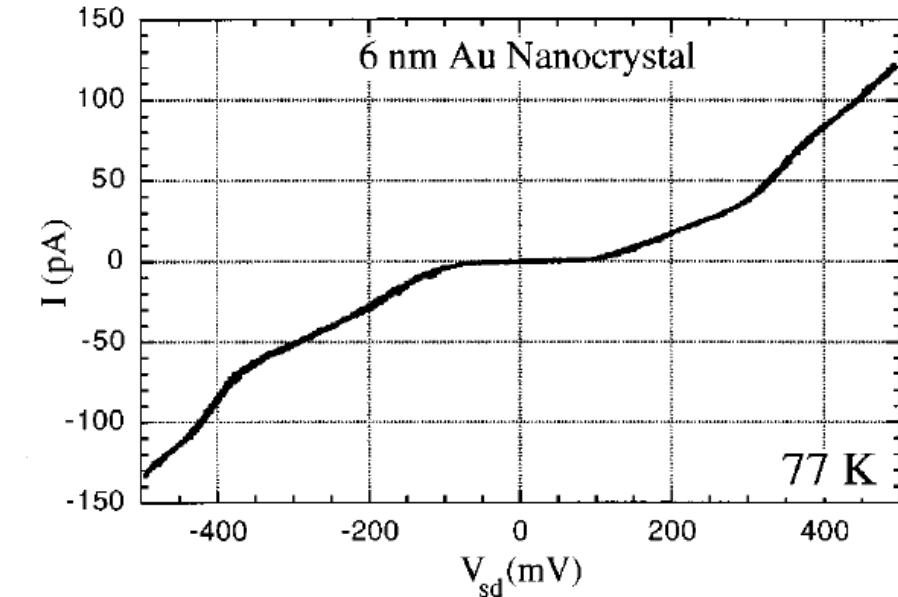
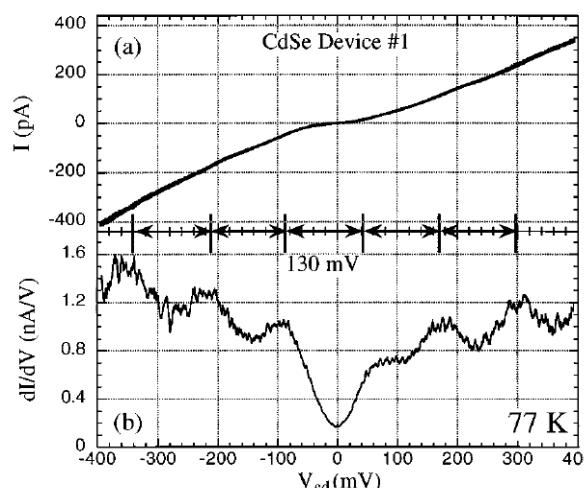
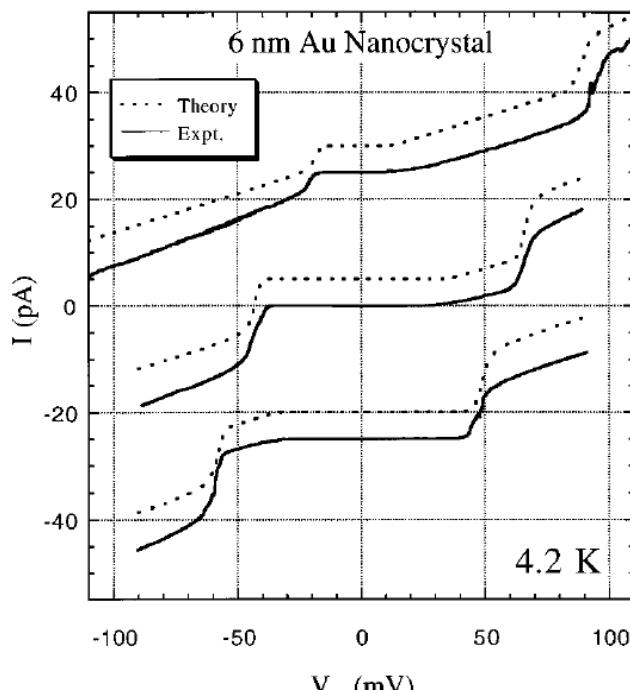
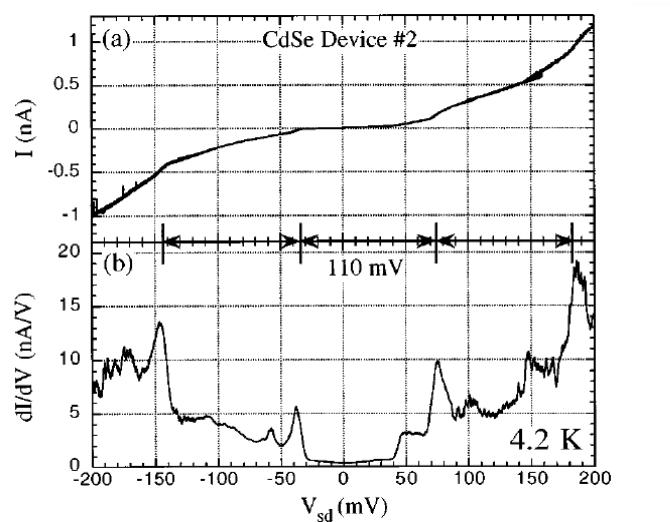
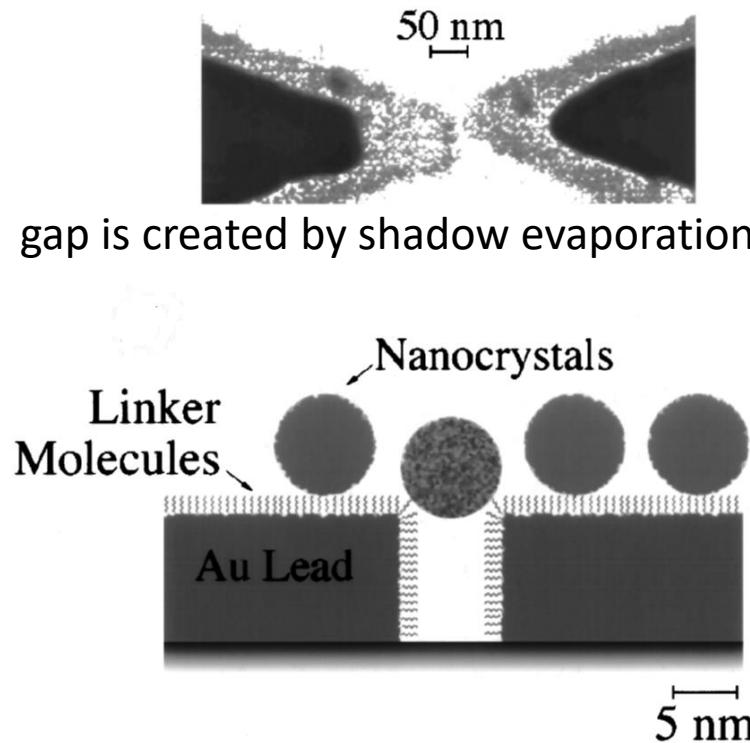
chlorosilane ($-\text{SiCl}_3$) hydrolysis products



1,6-hexanedithiol linker

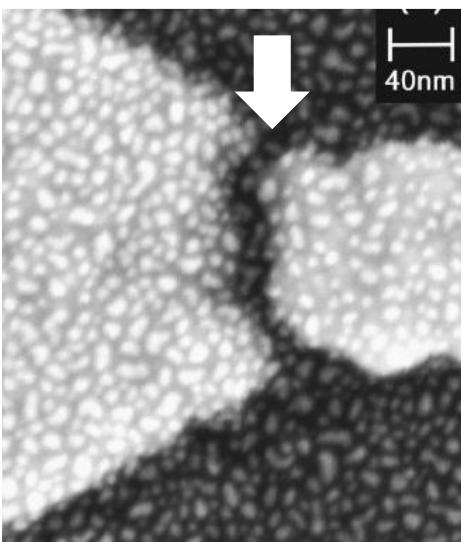
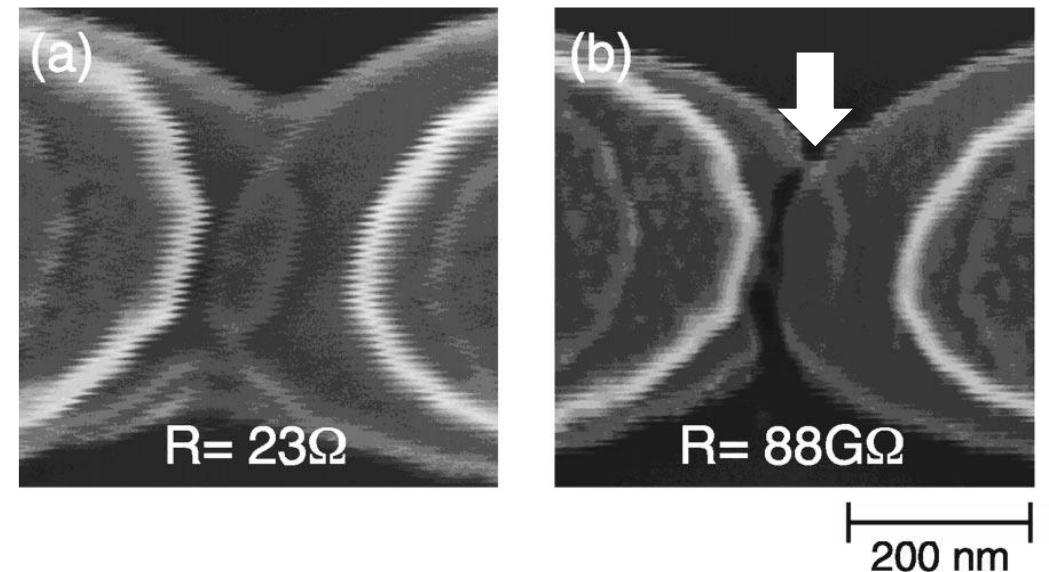
Appl. Phys. Lett 68 (1996) 2574

0D particles for single electron transfer



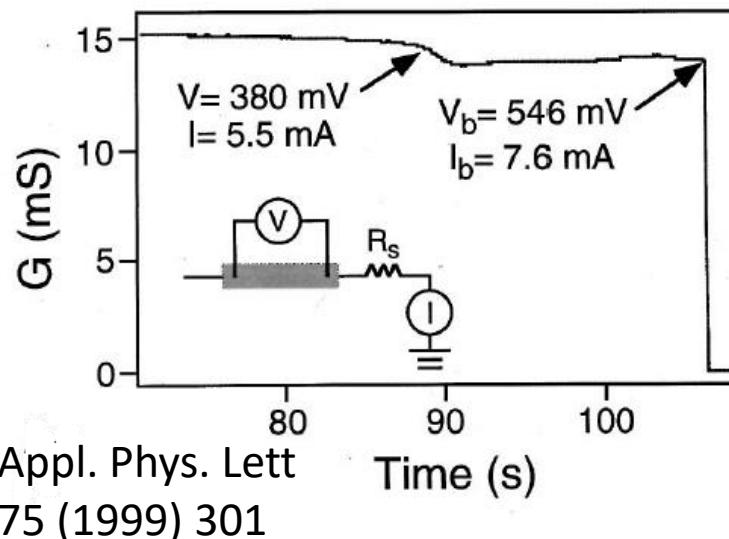
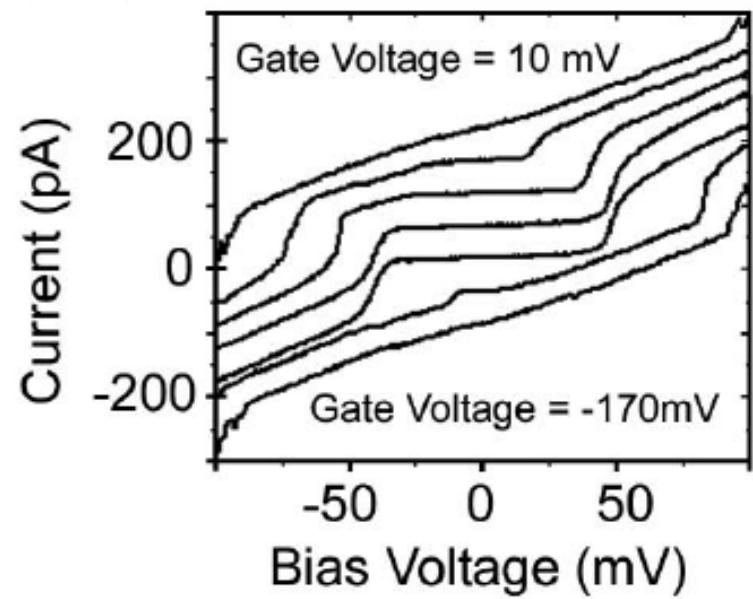
Appl. Phys. Lett 70 (1997) 2759

nm-size gaps: fabricated by electromigration, for single electron transistors

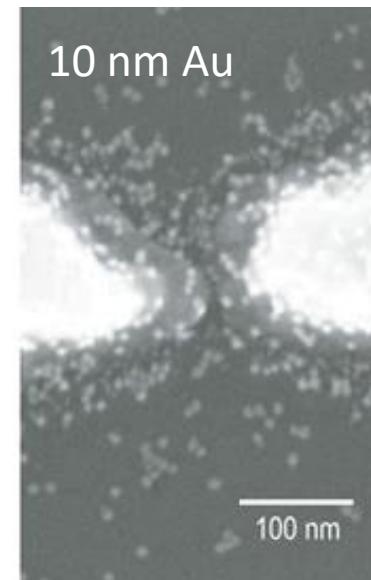
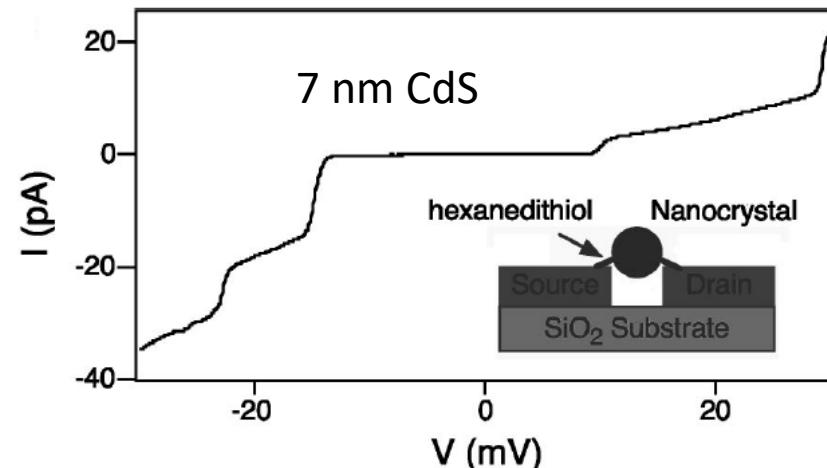


Appl. Phys. Lett
84 (2004) 3154

Evaporated Au islands, 5 - 15 nm



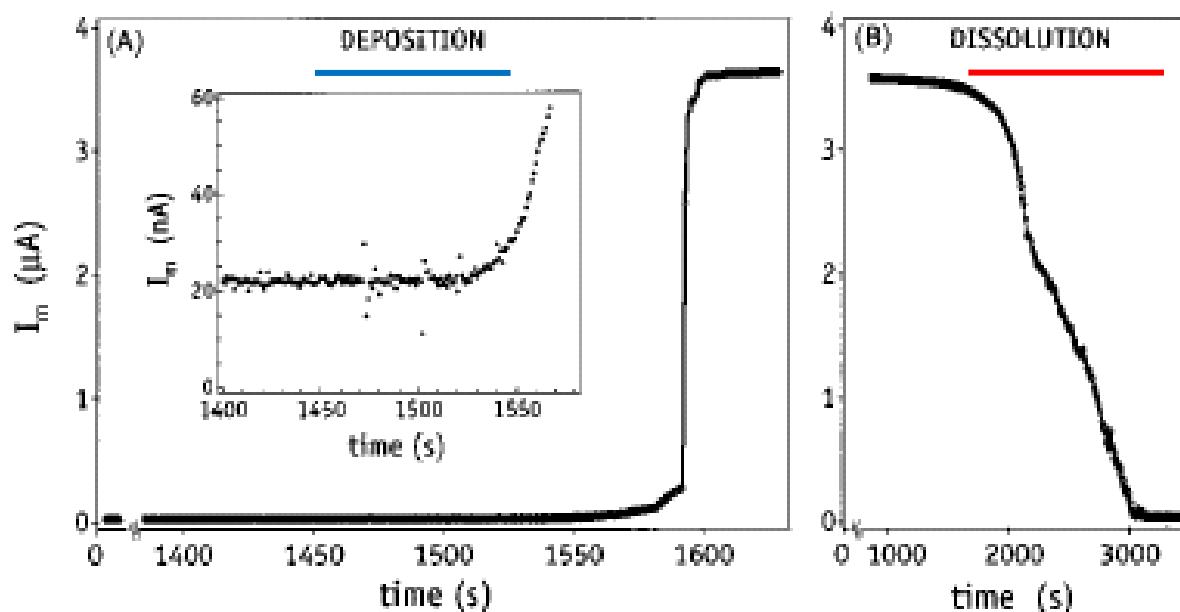
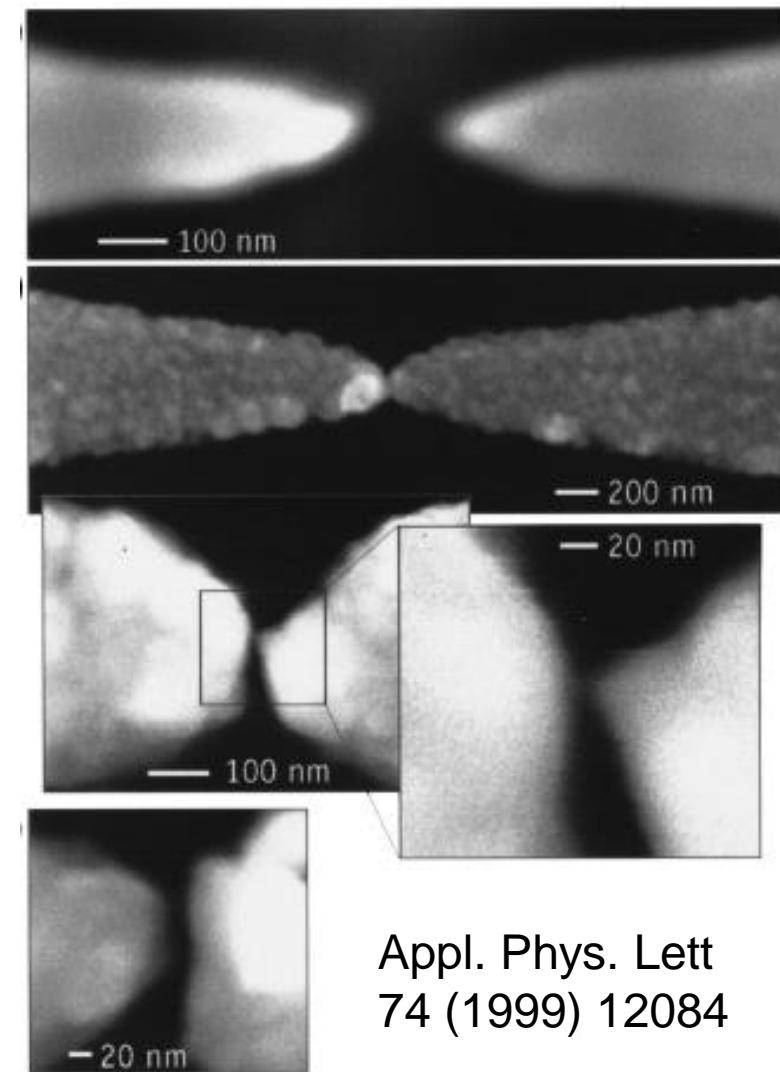
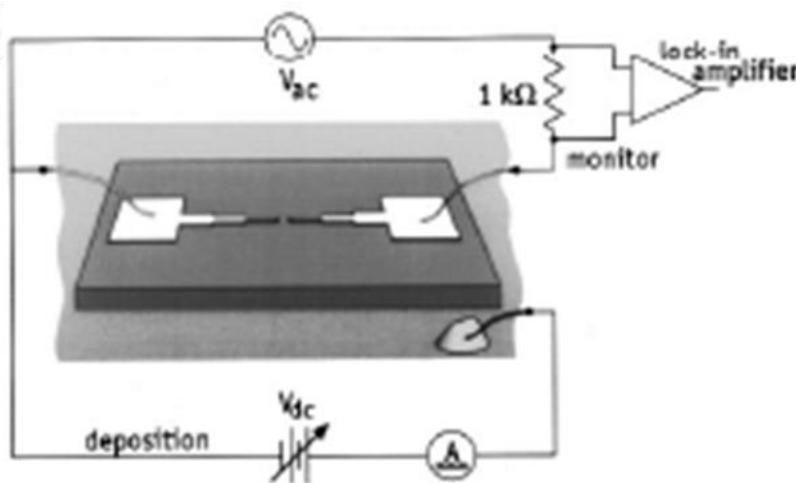
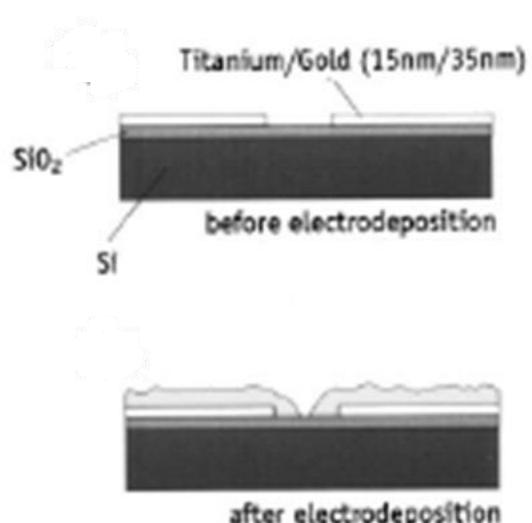
Appl. Phys. Lett
75 (1999) 301



5 nm gap,
aminosilane
linker

AIP Conf. Proc.
850 (2006) 1438

Gaps formed by electrodeposition and dissolution $[\text{Au}(\text{CN})_4]^- + 3 \text{ e} \rightleftharpoons \text{Au} + 4\text{CN}^-$



Appl. Phys. Lett.
74 (1999) 12084

Assembling: reviews

- A. Ulman, Formation and Structure of Self-Assembled Monolayers, *Chem. Rev.* 96 (1996) 1533-1554.
- D. L. Feldheim, C. D. Keating, Self-assembly of single electron transistors and related devices, *Chem. Soc. Rev.* 27 (1998) 1-12.
- S. P. Pujari, L. Scheres, A.T.M. Marcelis, H. Zuilhof, Covalent Surface Modification of Oxide Surfaces, *Angew. Chem. Int. Ed.* 53 (2014) 6322-6356.
- K.S. Novoselov, A. Mishchenko, A.Carvalho,A.H.CastroNeto, *Science* 353 (2016) No aac9439.
- C. Klinke, Electrical transport through self-assembled colloidal nanomaterials and their perspectives, *EPL* 119 (2017) No 36002.
- R. Frisenda, E. Navarro-Moratalla, P. Gant et al., Recent progress in the assembly of nanodevices and van der Waals heterostructures by deterministic placement of 2D materials, *Chem. Soc. Rev.* 47 (2018) 53-68.
- Z. Lin, Y. Huang, X. Duan, Van der Waals thin-film electronics, *Nature Electronics* 2 (2019) 378-388.
- M. Onodera, S. Masubuchi, R. Moriya, T. MacHida, *Jap. J. Appl. Phys.* 59 (2020) No 010101.
- M.T. Rabbani, M. Sonker, A. Ros, Carbon nanotube dielectrophoresis: Theory and applications, *Electrophoresis* 41 (2020) 1893–1914.
- Z. Zhang, Z. Tian, Y. Mei, Z. Di, Shaping and structuring 2D materials via kirigami and origami, *Mater. Sci. Eng. R* 145 (2021) No 100621.
- J. Kim, O. Song, Y. S. Cho et al., Revisiting Solution-Based Processing of van der Waals Layered Materials for Electronics, *ACS Mater. Au* 2 (2022) 382–393.
- P. V. Pham, S. C. Bodepudi, K. Shehzad et al., *Chem. Rev.* 122 (2022) 6514-6613.
- W. Liu, Y. Yu, M. Peng et al., Integrating 2D layered materials with 3D bulk materials as van der Waals heterostructures for photodetections: Current status and perspectives, *InfoMat* 5 (2023) No e12470.